

# USB Power Delivery 4-Switch Buck Boost Controller

## NCV81599, NCP81599

The NCV81599 USB Power Delivery (PD) Controller is a synchronous buck boost that is optimized for converting battery voltage or adaptor voltage into power supply rails required in notebook, tablet, and desktop systems, as well as many other consumer devices using USB PD standard and C-Type cables. The NCV81599 is fully compliant to the USB Power Delivery Specification when used in conjunction with a USB PD or C-Type Interface Controller. NCV81599 is designed for applications requiring dynamically controlled slew rate limited output voltage that require either voltage higher or lower than the input voltage. The NCV81599 drives 4 NMOSFET switches, allowing it to buck or boost and support the functions specified in the USB Power Delivery Specification which is suitable for all USB PD applications. The USB PD Buck Boost Controller operates with a supply and load range of 4.5 V to 32 V.

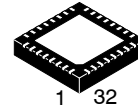
### Features

- Wide Input Voltage Range:  
from 4.5 V to 32 V for NCV81599  
from 4.5 V to 30 V for NCP81599
- Dynamically Programmed Frequency from 150 kHz to 1.2 MHz
- I<sup>2</sup>C Interface
- Real Time Power Good Indication
- Controlled Slew Rate Voltage Transitioning
- Feedback Pin with Internally Programmed Reference
- Support USBPD/QC2.0/QC3.0 Profile
- 2 Independent Current Sensing Inputs
- Over Temperature Protection
- Adaptive Non-Overlap Gate Drivers
- Audible Range Switching Frequency Avoidance
- Over-Voltage and Over-Current Protection
- AEC-Q100 Qualified (NCV81599)
- 5 x 5 mm QFN32 Package

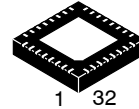
### ORDERING INFORMATION

| Device        | Package            | Shipping <sup>†</sup> |
|---------------|--------------------|-----------------------|
| NCV81599MWTXG | QFN32<br>(Pb-Free) | 5000 / Tape & Reel    |
| NCP81599MNTXG | QFN32<br>(Pb-Free) | 2500 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

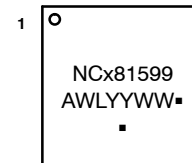


QFN32 5x5, 0.5P  
CASE 485CE  
(NCP81599)



QFNW32 5x5, 0.5P  
CASE 484AB  
(NCV81599)

### MARKING DIAGRAM



NCx81599 = Specific Device Code

x = V or P  
A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### Typical Application

- Automotive USB Charging Ports
- Wireless Charging
- Consumer Electronics

NCV81599, NCP81599

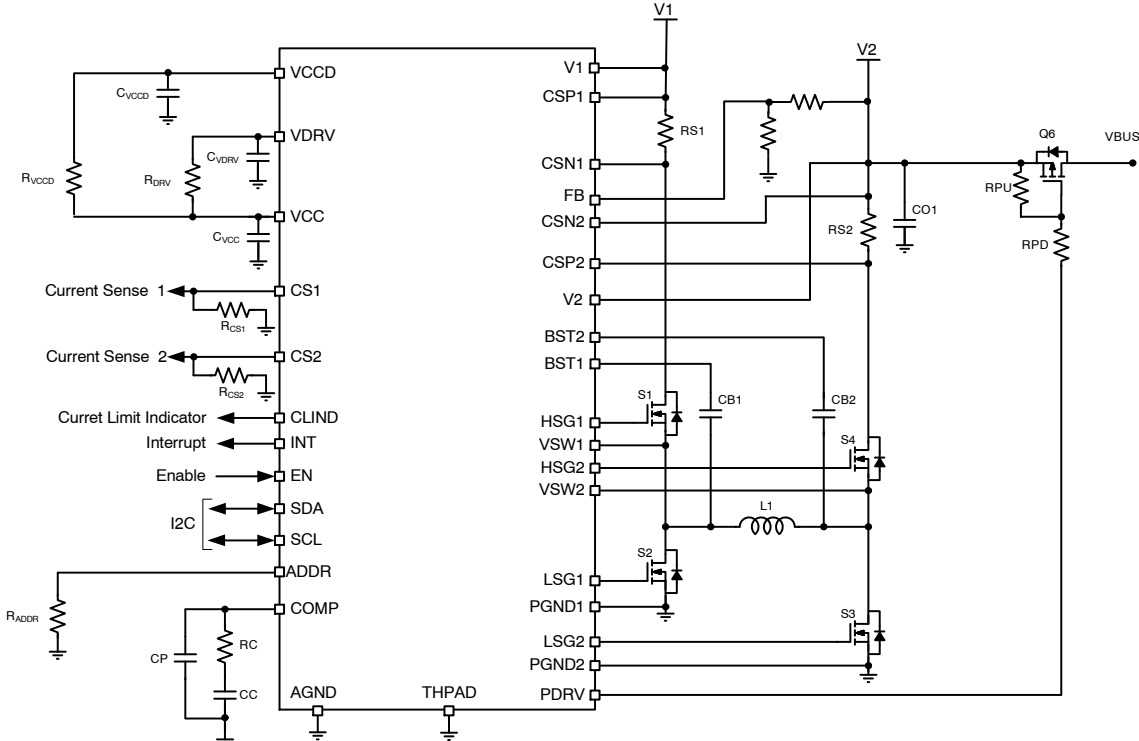


Figure 1. Typical Application Circuit

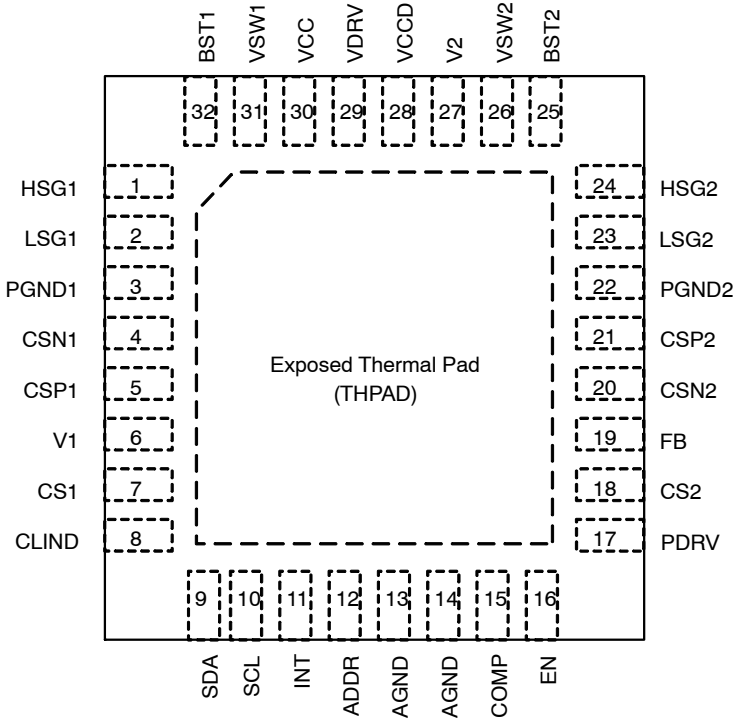
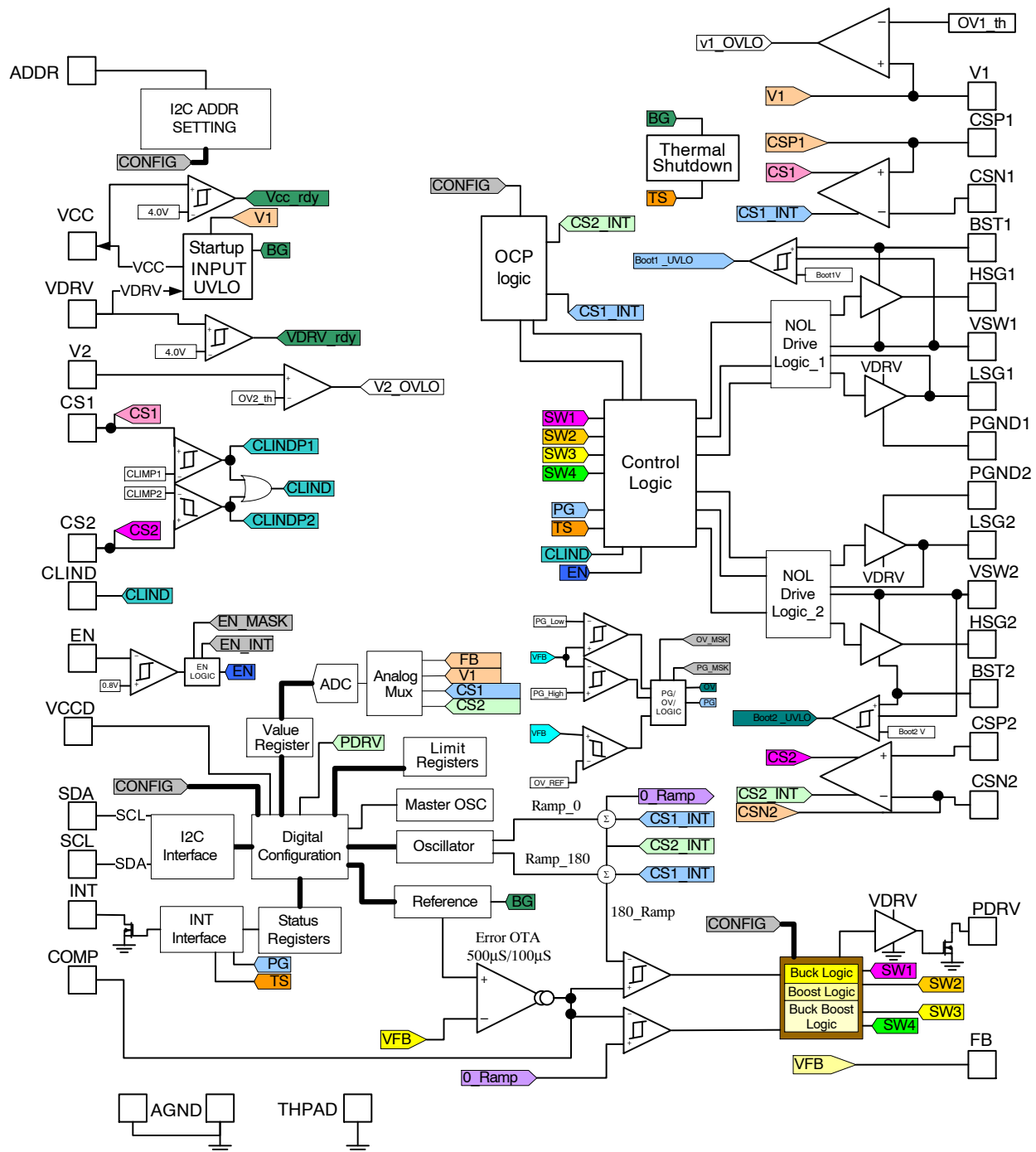


Figure 2. Pinout



# NCV81599, NCP81599

**Table 1. PIN FUNCTION DESCRIPTION**

| Pin   | Pin Name | Description                                                                                                                                                                                                              |
|-------|----------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1     | HSG1     | S1 gate drive. Drives the S1 N-channel MOSFET with a voltage equal to VDRV superimposed on the switch node voltage VSW1.                                                                                                 |
| 2     | LSG1     | Drives the gate of the S2 N-channel MOSFET between ground and VDRV.                                                                                                                                                      |
| 3, 22 | PGND     | Power ground for the low side MOSFET drivers. Connect these pins closely to the source of the bottom N-channel MOSFETs.                                                                                                  |
| 4     | CSN1     | Negative terminal of the current sense amplifier.                                                                                                                                                                        |
| 5     | CSP1     | Positive terminal of the current sense amplifier.                                                                                                                                                                        |
| 6     | V1       | Input voltage of the converter                                                                                                                                                                                           |
| 7     | CS1      | Current sense amplifier output. CS1 will source a current that is proportional to the voltage across RS1 to an external resistor. CS1 voltage can be monitored with a high impedance input. Ground this pin if not used. |
| 8     | CLIND    | Open drain output, high voltage on CLIND pin indicates that the CS1 or CS2 voltage has exceeded the I <sup>2</sup> C programmed limit.                                                                                   |
| 9     | SDA      | I <sup>2</sup> C interface data line.                                                                                                                                                                                    |
| 10    | SCL      | I <sup>2</sup> C interface clock line.                                                                                                                                                                                   |
| 11    | INT      | Interrupt is an open drain output that indicates the state of the output power, the internal thermal trip, and other I <sup>2</sup> C programmable functions.                                                            |
| 12    | ADDR     | I <sup>2</sup> C address pin, placing a less than 200 k $\Omega$ resistor to the ground to set the I <sup>2</sup> C address.                                                                                             |
| 13-14 | AGND     | The ground pin for the analog circuitry.                                                                                                                                                                                 |
| 15    | COMP     | Output of the transconductance amplifier used for stability in closed loop operation.                                                                                                                                    |
| 16    | EN       | Logic high enables the switching and logic low shuts down and reset the device. Middle level makes the device to stop switching and keep the VCC alive.                                                                  |
| 17    | PDRV     | The open drain output used to control a PMOSFET.                                                                                                                                                                         |
| 18    | CS2      | Current sense amplifier output. CS2 will source a current that is proportional to the voltage across RS2 to an external resistor. CS2 voltage can be monitored with a high impedance input. Ground this pin if not used. |
| 19    | FB       | Feedback voltage of the output, negative terminal of the gm amplifier.                                                                                                                                                   |
| 20    | CSN2     | Negative terminal of the current sense amplifier.                                                                                                                                                                        |
| 21    | CSP2     | Positive terminal of the current sense amplifier.                                                                                                                                                                        |
| 23    | LSG2     | Drives the gate of the S3 N-channel MOSFET between ground and VDRV.                                                                                                                                                      |
| 24    | HSG2     | S4 gate drive. Drives the S4 N-channel MOSFET with a voltage equal to VDRV superimposed on the switch node voltage VSW2.                                                                                                 |
| 25    | BST2     | Bootstrapped Driver Supply. The BST2 pin swings from a forward voltage drop below VDRV up to a forward voltage drop below VOUT + VDRV. Place a 0.1 $\mu$ F capacitor from this pin to VSW2.                              |
| 26    | VSW2     | Switch Node. VSW2 pin swings from a diode voltage drop below ground up to output voltage.                                                                                                                                |
| 27    | V2       | Output voltage of the converter. Connect to the output externally for OVLO sense.                                                                                                                                        |
| 28    | VCCD     | Internal digital power supply input. Always connect VCCD to VCC. A 1 $\mu$ F capacitor should be placed close to the part to decouple this line.                                                                         |
| 29    | VDRV     | Internal voltage supply to the driver circuits. A 1 $\mu$ F capacitor should be placed close to the part to decouple this line.                                                                                          |
| 30    | VCC      | The VCC pin supplies power to the internal circuitry. The VCC is the output of a linear regulator which is powered from V1. Pin should be decoupled with a 1 $\mu$ F capacitor for stable operation.                     |
| 31    | VSW1     | Switch Node. VSW1 pin swings from a diode voltage drop below ground up to V1.                                                                                                                                            |
| 32    | BST1     | Bootstrapped Driver Supply. The BST1 pin swings from a forward voltage drop below VDRV up to a forward voltage drop below V1 + VDRV. Place a 0.1 $\mu$ F capacitor from this pin to VSW1.                                |
| 33    | THPAD    | Center Thermal Pad. Connect to AGND externally.                                                                                                                                                                          |

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**Table 2. MAXIMUM RATINGS**

Over operating free-air temperature range unless otherwise noted

| Rating                                                                            | Symbol         | Min                               | Max                   | Unit |
|-----------------------------------------------------------------------------------|----------------|-----------------------------------|-----------------------|------|
| VCCD Input Voltage                                                                | VCCD           | −0.3                              | 5.5                   | V    |
| Address Pin Output Voltage                                                        | ADDR           | −0.3                              | 5.5                   | V    |
| Driver Input Voltage                                                              | VDRV           | −0.3                              | 5.5                   | V    |
| Internal Regulator Output                                                         | VCC            | −0.3                              | 5.5                   | V    |
| Output of Current Sense Amplifiers                                                | CS1, CS2       | −0.3                              | 5.5                   | V    |
| Current Limit Indicator                                                           | CLIND          | −0.3                              | VCC + 0.3             | V    |
| Interrupt Indicator                                                               | INT            | −0.3                              | VCC + 0.3             | V    |
| Enable Input                                                                      | EN             | −0.3                              | 5.5                   | V    |
| I <sup>2</sup> C Communication Lines                                              | SDA, SCL       | −0.3                              | VCC + 0.3             | V    |
| Compensation Output                                                               | COMP           | −0.3                              | VCC + 0.3             | V    |
| V1 Power Stage Input Voltage                                                      | V1             | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Positive Current Sense                                                            | CSP1           | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Negative Current Sense                                                            | CSN1           | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Positive Current Sense                                                            | CSP2           | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Negative Current Sense                                                            | CSN2           | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Feedback Voltage                                                                  | FB             | −0.3                              | 5.5                   | V    |
| Driver 1 and Driver 2 Positive Rails                                              | BST1,<br>BST2  | −0.3 V wrt/PGND<br>−0.3 V wrt/VSW | 40 V<br>5.5 V wrt/VSW | V    |
| High Side Driver 1 and Driver 2                                                   | HSG1,<br>HSG2  | −0.3 V wrt/PGND<br>−0.3 V wrt/VSW | 40 V<br>5.5 V wrt/VSW | V    |
| Switching Nodes and Return Path of Driver 1 and Driver 2                          | VSW1, VSW2     | −2.0 V,<br>−5 V (100 ns)          | 35 V, 40 V (20 ns)    | V    |
| Low Side Driver 1 and Driver 2                                                    | LSG1, LSG2     | −0.3 V                            | 5.5                   | V    |
| PMOSFET Driver                                                                    | PDRV           | −0.3                              | 35 V, 40 V (20 ns)    | V    |
| Voltage Differential                                                              | AGND to PGND   | −0.3                              | 0.3                   | V    |
| CSP1–CSN1, CSP2–CSN2 Differential Voltage                                         | CS1DIF, CS2DIF | −0.5                              | 0.5                   | V    |
| PDRV Maximum Current                                                              | PDRV1          | 0                                 | 10                    | mA   |
| PDRV Maximum Pulse Current<br>(100 ms on time, with > 1 s interval)               | PDRV1PUL       | 0                                 | 200                   | mA   |
| Maximum VCC Current                                                               | VCCI           | 0                                 |                       | mA   |
| Operating Junction Temperature Range (Note 1)                                     | TJ             | −40                               | 150                   | °C   |
| Operating Ambient Temperature Range                                               | TA             | −40                               | 125                   | °C   |
| Storage Temperature Range                                                         | TSTG           | −55                               | 150                   | °C   |
| Thermal Characteristics (Note 2)<br>QFN 32 5mm x 5mm                              |                |                                   |                       |      |
| Maximum Power Dissipation @ TA = 25°C                                             | PD             |                                   | 4.1                   | W    |
| Maximum Power Dissipation @ TA = 85°C                                             | PD             |                                   | 2.1                   | W    |
| Thermal Resistance Junction–to–Air with Solder                                    | RθJA           |                                   | 30                    | °C/W |
| Thermal Resistance Junction–to–Case Top with Solder                               | RθJCT          |                                   | 1.7                   | °C/W |
| Thermal Resistance Junction–to–Case Bottom with Solder                            | RθJCB          |                                   | 2.0                   | °C/W |
| Lead Temperature Soldering (10 sec):<br>Reflow (SMD styles only) Pb–Free (Note 3) | RF             | 260 Peak                          |                       | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The maximum package power dissipation limit must not be exceeded.
2. The value of  $\theta_{JA}$  is measured with the device mounted on a 3in x 3in, 4 layer, 0.062 inch FR-4 board with 1.5 oz. copper on the top and bottom layers and 0.5 ounce copper on the inner layers, in a still air environment with TA = 25°C.
3. 60–180 seconds minimum above 237°C.

# NCV81599, NCP81599

**Table 3. ELECTRICAL CHARACTERISTICS**

(V1 = 12 V, V<sub>out</sub> = 5 V, T<sub>A</sub> = +25°C for typical value; -40°C < T<sub>A</sub> = T<sub>J</sub> < 125°C for min/max values unless noted otherwise)

| Parameter                                        | Symbol               | Test Conditions                                        | Min        | Typ  | Max      | Units   |
|--------------------------------------------------|----------------------|--------------------------------------------------------|------------|------|----------|---------|
| <b>POWER SUPPLY</b>                              |                      |                                                        |            |      |          |         |
| V1 Operating Input Voltage                       | V1                   | NCV81599                                               | 4.5        |      | 32       | V       |
|                                                  |                      | NCP81599                                               | 4.5        |      | 30       |         |
| VDRV Operating Input Voltage                     | VDRV                 |                                                        | 4.5        | 5    | 5.5      | V       |
| VCCD Operating Input Voltage                     | VCCD                 |                                                        | 4.5        |      | 5.5      | V       |
| VCC UVLO Rising Threshold                        | VCC <sub>RISE</sub>  |                                                        | 4.21       | 4.27 | 4.35     | V       |
| VCC UVLO Falling Threshold                       | VCC <sub>FALL</sub>  |                                                        | 3.90       | 3.96 | 4.06     | V       |
| UVLO Hysteresis for VCC                          | VCCV <sub>HYS</sub>  | Falling Hysteresis                                     |            | 300  |          | mV      |
| VDRV UVLO Rising Threshold                       | VDRV <sub>RISE</sub> |                                                        | 4.21       | 4.31 | 4.35     | V       |
| VDRV UVLO Falling Threshold                      | VDRV <sub>FALL</sub> |                                                        | 3.90       | 4.01 | 4.06     | V       |
| VDRV UVLO Hysteresis                             | VDRV <sub>HYS</sub>  |                                                        |            | 300  |          | mV      |
| VCC Output Voltage                               | VCC                  | With no external load                                  | 4.5        | 5    |          | V       |
| VCC Drop Out Voltage                             | VCCDROOP             | 30 mA load                                             |            | 100  |          | mV      |
| VCC Output Current Limit                         | IOUT <sub>VCC</sub>  | VCC Loaded to 4.3 V, EN > 0.8 V                        | 80         | 97   |          | mA      |
| VCC Short Current Limit                          | IVCC_SHORT           | VCC short                                              |            | 14.6 |          | mA      |
| V1 Shutdown Supply Current                       | IVCC_SD              | EN < 0.4 V, V1 = 12 V                                  |            | 8.0  | 15       | μA      |
| V1 Normal Current                                | IV1                  | 0.8 V < EN < 1.88 V, 4.5 V ≤ V1 ≤ 32 V, (No Switching) |            | 7.3  |          | mA      |
| VCCD Standby Current                             | IVCCD                | 0.8 V < EN < 1.88 V                                    |            | 4    |          | mA      |
| VCCD Switching Current                           | IVCCD_SW             | EN > 2.2 V                                             |            | 4.1  |          | mA      |
| VDRIVE Switching Current Buck                    | IV1_SW               | EN = 5 V, Cgate = 2.2 nF, VSW = 0 V, FSW = 600 kHz     |            | 16   |          | mA      |
| VDRIVE Switching Current Boost                   | IV1_SW               | EN = 5 V, Cgate = 2.2 nF, VSW = 0 V, FSW = 600 kHz     |            | 15   |          | mA      |
| <b>VOLTAGE OUTPUT</b>                            |                      |                                                        |            |      |          |         |
| Voltage Output Accuracy                          | FB                   | DAC_TARGET = 00110010                                  | 0.495      | 0.5  | 0.505    | V       |
|                                                  |                      | DAC_TARGET = 01111000                                  | 1.188      | 1.2  | 1.212    |         |
|                                                  |                      | DAC_TARGET = 11001000                                  | 1.98       | 2.0  | 2.02     |         |
| Voltage Accuracy Over Temperature                | VOUTERT              | VFB ≥ 0.5 V<br>VFB < 0.5 V                             | -1.0<br>-5 |      | 1.0<br>5 | %<br>mV |
|                                                  | VOUTER               | T <sub>A</sub> = 25°C<br>VFB ≥ 0.5 V                   | -0.45      |      | 0.45     | %       |
| <b>TRANSCONDUCTANCE AMPLIFIER</b>                |                      |                                                        |            |      |          |         |
| Gain Bandwidth Product                           | GBW                  | (Note 4)                                               |            | 5.2  |          | MHz     |
| Transconductance                                 | GM1                  | Default                                                |            | 500  |          | μS      |
| Max Output Source Current limit                  | GMSOC                |                                                        | 60         | 80   |          | μA      |
| Max Output Sink Current limit                    | GMSIC                |                                                        | 60         | 80   |          | μA      |
| Voltage Ramp                                     | Vramp                |                                                        |            | 1.2  |          | V       |
| <b>INTERNAL BST SWITCH</b>                       |                      |                                                        |            |      |          |         |
| Pass FET Rds(on)                                 | RBST                 | I <sub>F</sub> = 1 mA                                  |            | 60   |          | Ω       |
| Reverse Leakage Current from BST pin to VDRV pin | DIL                  | BST = 32 V, T <sub>A</sub> = 25°C                      |            | 0.05 | 1        | μA      |
| BST-VSW UVLO                                     | BST_UVLO             | Falling                                                | 3.2        | 3.5  | 3.8      | V       |
| BST-VSW UVLO                                     | BST_UVLO             | Rising                                                 | 3.4        | 3.7  | 4.1      | V       |

4. Ensured by design. Not production tested.

5. Typical value only. Not production tested.

# NCV81599, NCP81599

**Table 3. ELECTRICAL CHARACTERISTICS** (continued)

(V<sub>I</sub> = 12 V, V<sub>out</sub> = 5 V, T<sub>A</sub> = +25°C for typical value; -40°C < T<sub>A</sub> = T<sub>J</sub> < 125°C for min/max values unless noted otherwise)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
|-----------|--------|-----------------|-----|-----|-----|-------|
|-----------|--------|-----------------|-----|-----|-----|-------|

## INTERNAL BST SWITCH

|                    |         |          |  |     |  |    |
|--------------------|---------|----------|--|-----|--|----|
| BST-VSW Hysteresis | BST_HYS | (Note 4) |  | 200 |  | mV |
|--------------------|---------|----------|--|-----|--|----|

## OSCILLATOR

|                               |                  |                                        |     |      |     |     |
|-------------------------------|------------------|----------------------------------------|-----|------|-----|-----|
| Oscillator Frequency          | FSW_0            | FSW = 001 (Note 5)                     |     | 150  |     | kHz |
|                               |                  | FSW = 000, default                     | 552 | 600  | 648 |     |
|                               |                  | FSW = 010                              |     | 300  |     |     |
|                               |                  | FSW = 011                              |     | 450  |     |     |
|                               |                  | FSW = 100                              |     | 740  |     |     |
|                               |                  | FSW = 101                              |     | 880  |     |     |
|                               |                  | FSW = 110                              |     | 1145 |     |     |
| Oscillator Frequency Accuracy | FSWE             |                                        | -12 |      | 12  | %   |
| Minimum On Time               | MOT              | Measured at 10% to 90% of VCC (Note 4) |     | 100  |     | ns  |
| Minimum Off Time              | MOFT             | Measured at 90% to 10% of VCC (Note 4) |     | 100  |     | ns  |
| Minimum Switching Frequency   | F <sub>MIN</sub> |                                        | 30  | 45   | 60  | kHz |

## INT THRESHOLDS

|                                |          |                                                           |     |           |     |    |
|--------------------------------|----------|-----------------------------------------------------------|-----|-----------|-----|----|
| Interrupt Low Voltage          | VINTI    | IINT(sink) = 2 mA                                         |     |           | 0.2 | V  |
| Interrupt High Leakage Current | INII     | 5 V                                                       |     | 3         | 100 | nA |
| Interrupt Startup Delay        | INTPG    | Soft Start end to PG positive edge                        |     | 2.1       |     | ms |
| Interrupt Propagation Delay    | PGI      | Delay for power good in                                   |     | 3.3       |     | ms |
|                                | PGO      | Delay for power good out                                  |     | 100       |     | ns |
| Power Good Threshold           | PGTH     | Power Good in from falling<br>Power Good out from falling |     | 104<br>93 |     | %  |
|                                | PGTH     | Power Good out from rising<br>Power Good in from rising   |     | 106<br>95 |     | %  |
| FB Overvoltage Threshold       | FB_OV    | V <sub>FB</sub> = 0.5 V                                   | 112 | 115       | 117 | %  |
|                                |          | V <sub>FB</sub> = 1.3 V                                   | 112 | 115       | 118 |    |
| Overvoltage Propagation Delay  | VFB_OVDL |                                                           |     | 1 Cycle   |     |    |

## EXTERNAL CURRENT SENSE (CS1,CS2)

|                                        |          |                                                                        |     |     |      |    |
|----------------------------------------|----------|------------------------------------------------------------------------|-----|-----|------|----|
| Positive Current Measurement High      | CS10     | CSP1-CSN1 or CSP2-CSN2 = 25 mV                                         |     | 125 |      | μA |
| Transconductance Gain Factor           | CSGT     | Current Sense Transconductance<br>V <sub>sense</sub> = 10 mV to 100 mV |     | 5   |      | mS |
| Transconductance Deviation             | CSGE     | CSPx-CSNx = 10 mV                                                      | -30 |     | 30   | %  |
|                                        |          | CSPx-CSNx = 25 mV to 100 mV                                            | -20 |     | 20   |    |
| Input Current Sense Common Mode Range  | CSCMMR_I | CSP1 is tied to V1                                                     | 4.5 |     | 32   | V  |
| Output Current Sense Common Mode Range | CSCMMR_O |                                                                        | 4   |     | 25.5 | V  |
| Input Sense Voltage Full Scale         | ISVFS    | (Note 4)                                                               |     |     | 100  | mV |
| CS Output Voltage Range                | CSOR     | VSENSE = 100 mV Rset = 6k (Note 4)                                     | 0   |     | 3    | V  |

## EXTERNAL CURRENT LIMIT (CLIND)

|                                                     |         |                        |  |     |     |    |
|-----------------------------------------------------|---------|------------------------|--|-----|-----|----|
| Current Limit Indicator Output Low                  | CLINDL  | Input current = 500 μA |  | 7.0 | 100 | mV |
| Current Limit Indicator Output High Leakage Current | ICLINDH | Pull up to 5 V         |  | 65  | 100 | nA |

4. Ensured by design. Not production tested.

5. Typical value only. Not production tested.

# NCV81599, NCP81599

**Table 3. ELECTRICAL CHARACTERISTICS** (continued)

(V<sub>1</sub> = 12 V, V<sub>out</sub> = 5 V, T<sub>A</sub> = +25°C for typical value; -40°C < T<sub>A</sub> = T<sub>J</sub> < 125°C for min/max values unless noted otherwise)

| Parameter                             | Symbol | Test Conditions                                            | Min | Typ                   | Max  | Units |
|---------------------------------------|--------|------------------------------------------------------------|-----|-----------------------|------|-------|
| <b>INTERNAL CURRENT SENSE</b>         |        |                                                            |     |                       |      |       |
| Internal Current Sense Gain for PWM   | ICG    | CSPx-CSNx = 25 mV                                          | 9.4 | 10                    | 10.5 | V/V   |
| Positive Peak Current Limit Trip      | PPCLT  | CLIP = 00 (default)<br>CLIP = 01<br>CLIP = 10<br>CLIP = 11 | 34  | 39<br>23<br>11<br>70  | 44   | mV    |
| Positive Peak Current Limit Latch-off | OCP_L  | CLIP = 00 (default)<br>CLIP = 01<br>CLIP = 10<br>CLIP = 11 |     | 70<br>39<br>23<br>106 |      | mV    |
| Negative Valley Current Limit Trip    | NVCLT  | CLIN = 00 (default)<br>CLIN = 01<br>CLIN = 10<br>CLIN = 11 | 34  | 40<br>25<br>15<br>0   | 45   | mV    |

## SWITCHING MOSFET DRIVERS

|                                   |         |                 |  |     |  |    |
|-----------------------------------|---------|-----------------|--|-----|--|----|
| HSG1 Pullup Resistance            | HSG1_PU | BST-VSW = 5 V   |  | 2   |  | Ω  |
| HSG1 Pulldown Resistance          | HSG1_PD | BST-VSW = 5 V   |  | 0.8 |  | Ω  |
| LSG1 Pullup Resistance            | LSG1_PU | LSG -PGND = 5 V |  | 2.4 |  | Ω  |
| LSG1 Pulldown Resistance          | LSG1_PD | LSG -PGND = 5 V |  | 0.7 |  | Ω  |
| HSG2 Pullup Resistance            | HSG2_PU | BST-VSW = 5 V   |  | 2.7 |  | Ω  |
| HSG2 Pulldown Resistance          | HSG2_PD | BST-VSW = 5 V   |  | 0.9 |  | Ω  |
| LSG2 Pullup Resistance            | LSG2_PU | LSG -PGND = 5 V |  | 2.0 |  | Ω  |
| LSG2 Pulldown Resistance          | LSG2_PD | LSG -PGND = 5 V |  | 0.7 |  | Ω  |
| HSG1 Falling to LSG1 Rising Delay | HSLSD1  |                 |  | 16  |  | ns |
| LSG1 Falling to HSG1 Rising Delay | LSHSD1  |                 |  | 36  |  | ns |
| HSG2 Falling to LSG2 Rising Delay | HSLSD2  |                 |  | 35  |  | ns |
| LSG2 Falling to HSG2 Rising Delay | LSHSD2  |                 |  | 56  |  | ns |

## SLEW RATE/SOFT START

|                                                  |       |                                                                                                              |  |                              |  |       |
|--------------------------------------------------|-------|--------------------------------------------------------------------------------------------------------------|--|------------------------------|--|-------|
| Charge Slew Rate<br>(VOUT measured at V2 pin)    | SLEWP | Slew = 00, FB = 0.1 VOUT<br>Slew = 01, FB = 0.1 VOUT<br>Slew = 10, FB = 0.1 VOUT<br>Slew = 11, FB = 0.1 VOUT |  | 0.6<br>1.2<br>2.4<br>4.8     |  | mV/μs |
| Discharge Slew Rate<br>(VOUT measured at V2 pin) | SLEWN | Slew = 00, FB = 0.1 VOUT<br>Slew = 01, FB = 0.1 VOUT<br>Slew = 10, FB = 0.1 VOUT<br>Slew = 11, FB = 0.1 VOUT |  | -0.6<br>-1.2<br>-2.4<br>-4.8 |  | mV/μs |

## ENABLE

|                                     |         |            |      |      |     |    |
|-------------------------------------|---------|------------|------|------|-----|----|
| EN LDO High Threshold Voltage       | ENLDOHT |            |      | 770  | 810 | mV |
| EN LDO Low Threshold Voltage        | ENLDOLT |            | 530  | 570  |     | mV |
| EN Switching High Threshold Voltage | ENHT    |            |      | 2.15 |     | V  |
| EN Switching Low Threshold Voltage  | ENLT    |            | 1.65 | 1.87 |     | V  |
| EN Pull Up Current (Default on)     | IEN_UP  | EN = 0.8 V |      | 3.0  |     | μA |

## ADDR

|                         |       |             |     |     |     |    |
|-------------------------|-------|-------------|-----|-----|-----|----|
| Internal Current Source | IADDR |             | 9   | 10  | 11  | μA |
| ADDR0                   |       | ADDR = 74 H |     |     | 110 | mV |
| ADDR1                   |       | ADDR = 75 H | 220 | 260 | 300 | mV |
| ADDR2                   |       | ADDR = 76 H | 380 | 440 | 500 | mV |

4. Ensured by design. Not production tested.

5. Typical value only. Not production tested.

# NCV81599, NCP81599

**Table 3. ELECTRICAL CHARACTERISTICS** (continued)

(V<sub>I</sub> = 12 V, V<sub>out</sub> = 5 V, T<sub>A</sub> = +25°C for typical value; -40°C < T<sub>A</sub> = T<sub>J</sub> < 125°C for min/max values unless noted otherwise)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
|-----------|--------|-----------------|-----|-----|-----|-------|
|-----------|--------|-----------------|-----|-----|-----|-------|

## ADDR

|       |  |             |     |     |     |    |
|-------|--|-------------|-----|-----|-----|----|
| ADDR3 |  | ADDR = 77 H | 600 | 715 | 830 | mV |
|-------|--|-------------|-----|-----|-----|----|

## I<sup>2</sup>C INTERFACE

|                           |          |  |  |     |   |     |
|---------------------------|----------|--|--|-----|---|-----|
| Voltage Threshold Rising  | I2CVTH_R |  |  | 1.2 |   | V   |
| Voltage Threshold Falling | I2CVTH_F |  |  | 0.9 |   | V   |
| Communication Speed       | I2CSP    |  |  |     | 1 | MHz |

## THERMAL SHUTDOWN

|                             |        |          |  |     |  |    |
|-----------------------------|--------|----------|--|-----|--|----|
| Thermal Shutdown Threshold  | TSD    | (Note 4) |  | 151 |  | °C |
| Thermal Shutdown Hysteresis | TSDHYS | (Note 4) |  | 28  |  | °C |

## PDRV

|                           |          |                       |   |      |    |    |
|---------------------------|----------|-----------------------|---|------|----|----|
| PDRV Operating Range      |          |                       | 0 |      | 32 | V  |
| PDRV Leakage Current      | PDRV_IDS | FET OFF, VPDRV = 32 V |   | 180  |    | nA |
| PDRV Drain-Source Voltage | PDRV_VDS | ISNK = 10 mA          |   | 0.20 |    | V  |

## INTERNAL ADC

|           |        |          |   |    |      |     |
|-----------|--------|----------|---|----|------|-----|
| Range     | ADCRN  | (Note 4) | 0 |    | 2.55 | V   |
| LSB Value | ADCLSB | (Note 4) |   | 20 |      | mV  |
| Error     | ADCFE  | (Note 4) |   | 1  |      | LSB |

## INPUT OVLO

|                                  |                       |          |  |      |  |    |
|----------------------------------|-----------------------|----------|--|------|--|----|
| Input OVLO Rising Threshold      | V <sub>OVLOIN_R</sub> |          |  | 34   |  | V  |
| Input OVLO Falling Threshold     | V <sub>OVLOIN_F</sub> |          |  | 28.5 |  | V  |
| Input OVLO Debounce Time         |                       | (Note 4) |  | 2    |  | μs |
| Input OVLO Recover Debounce Time |                       | (Note 4) |  | 1    |  | ms |

## OUTPUT OVLO

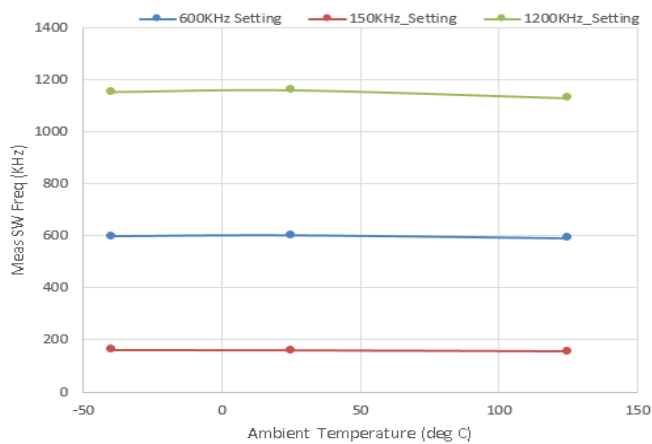
|                                                    |                     |                                                                            |  |                        |  |    |
|----------------------------------------------------|---------------------|----------------------------------------------------------------------------|--|------------------------|--|----|
| Output OVLO Threshold<br>(Register 06h, bit [5:4]) | V <sub>OVLO_O</sub> | sel_v2th = 00<br>sel_v2th = 01<br>sel_v2th = 10 (Default)<br>sel_v2th = 11 |  | 15<br>22.5<br>30<br>36 |  | V  |
| Output OVLO Debounce Time                          |                     | (Note 4)                                                                   |  | 1                      |  | μs |

4. Ensured by design. Not production tested.

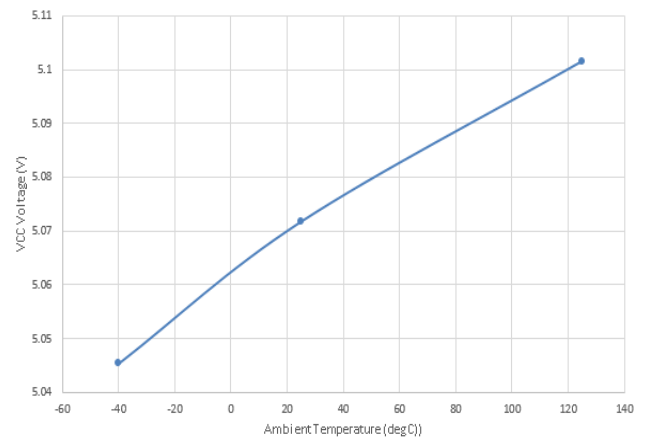
5. Typical value only. Not production tested.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

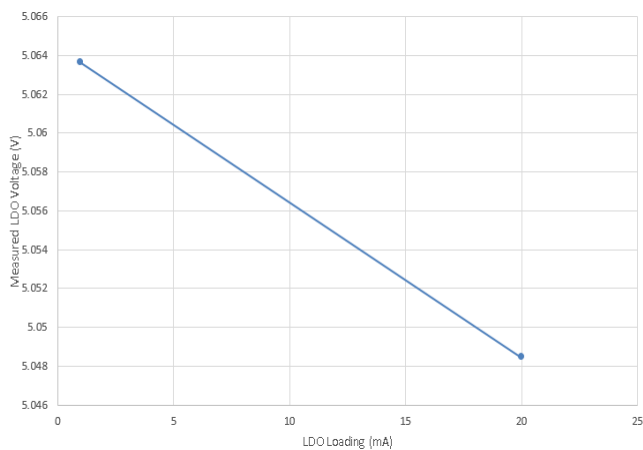
## TYPICAL CHARACTERISTICS



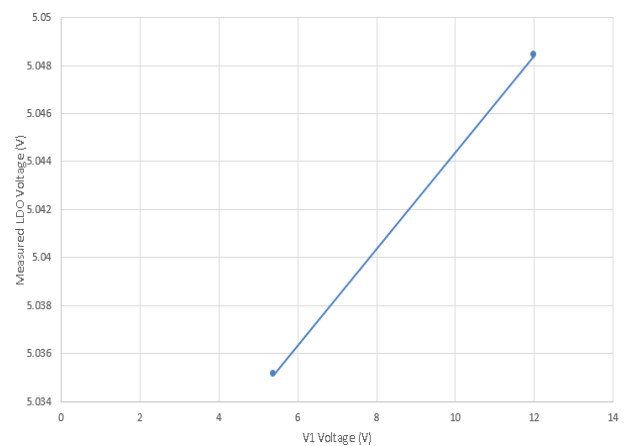
**Figure 1. Switching Frequency vs. Temperature**



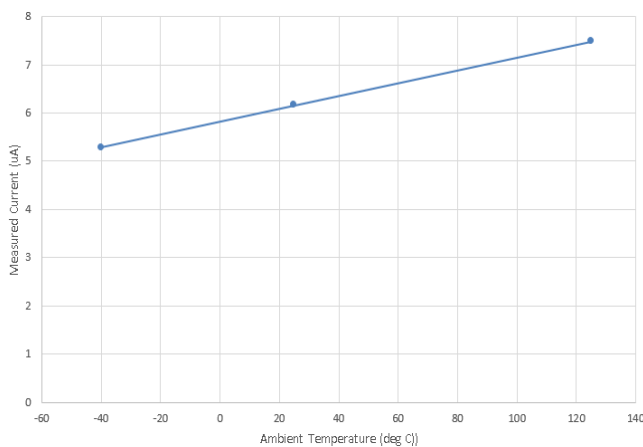
**Figure 2. VCC vs. Temperature**



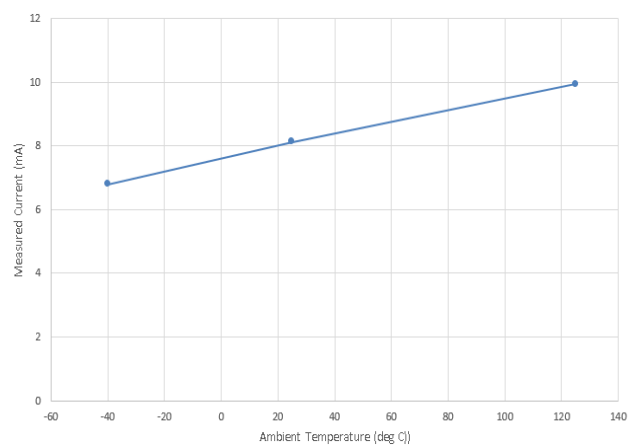
**Figure 3. VCC Load Regulation**



**Figure 4. VCC Line Regulation (20 mA Load)**



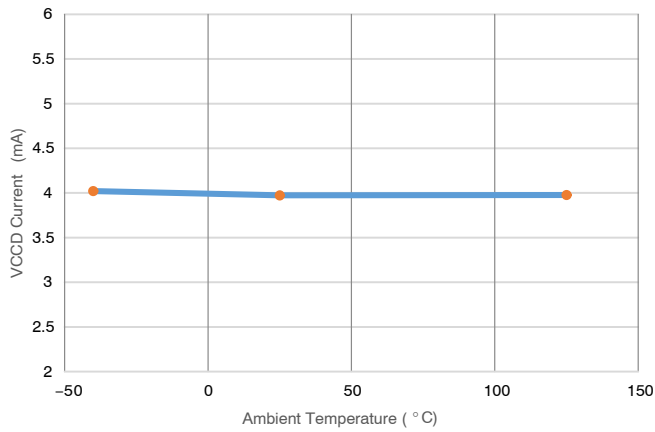
**Figure 5. Shutdown Supply Current vs. Temperature**



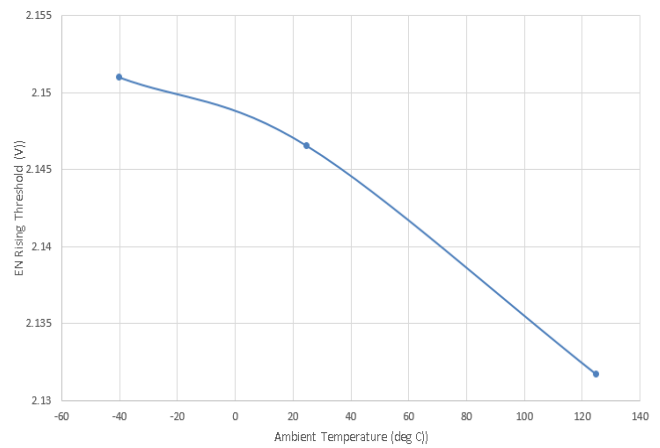
**Figure 6. V1 Normal Current vs. Temperature**

# NCV81599, NCP81599

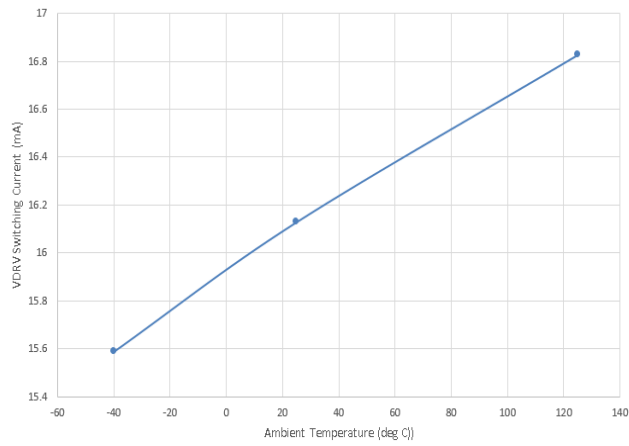
## TYPICAL CHARACTERISTICS



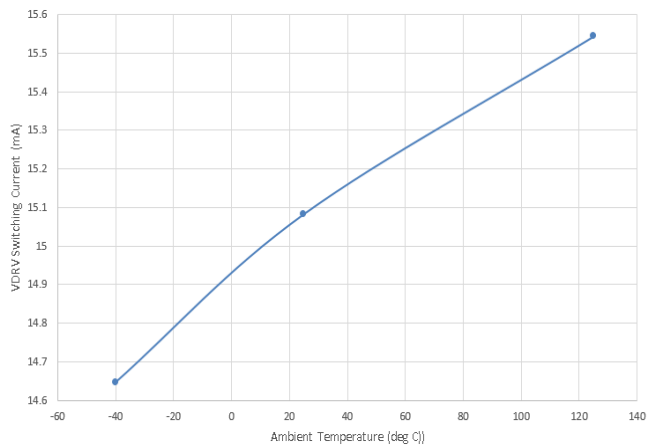
**Figure 7. VCCD Current vs. Temperature, VCCD = 5.0 V**



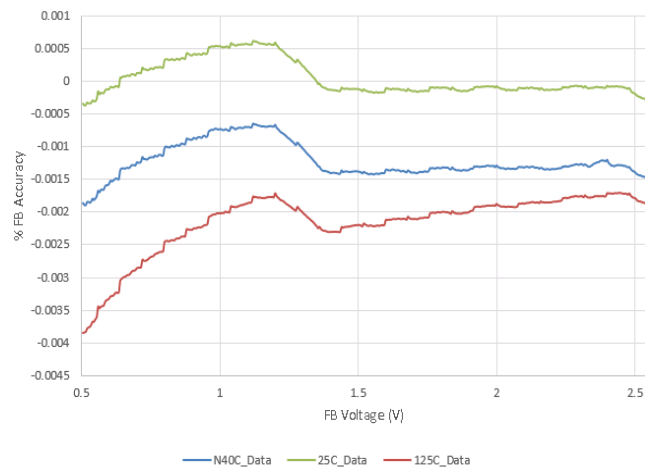
**Figure 8. ENABLE Rising Threshold vs. Temperature**



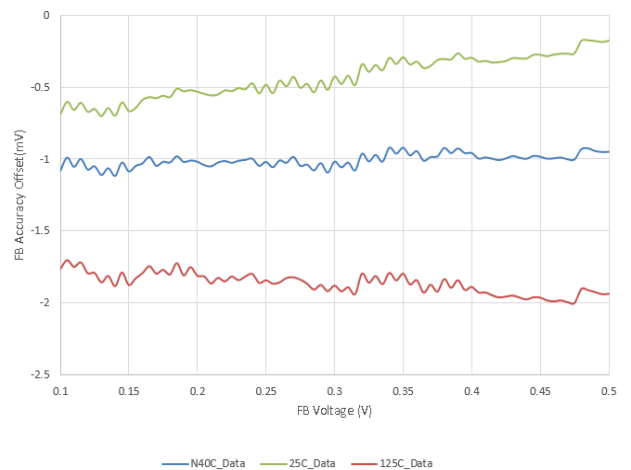
**Figure 9. VDRIVE Switching Current Buck vs. Temperature**



**Figure 10. VDRIVE Switching Current Boost vs. Temperature**

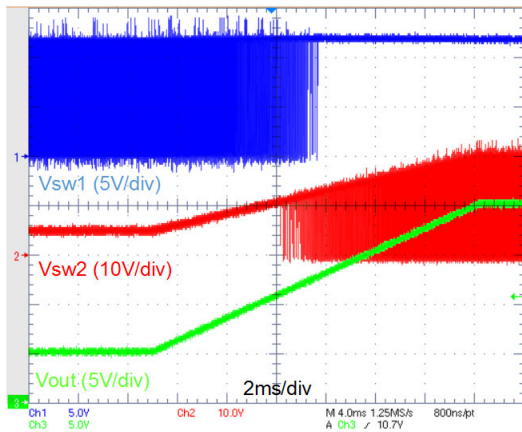


**Figure 11. Voltage Accuracy vs. Temperature (FB Setting > 500 mV)**



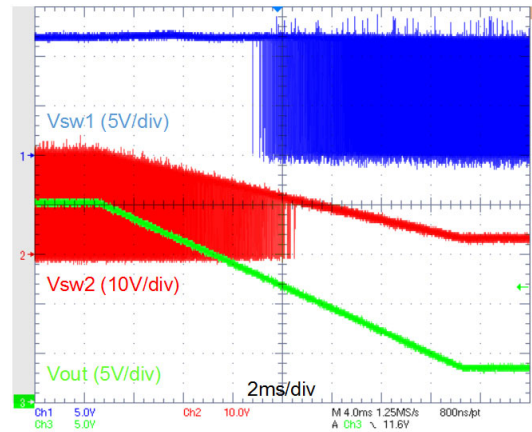
**Figure 12. Voltage Accuracy vs. Temperature**

TYPICAL CHARACTERISTICS



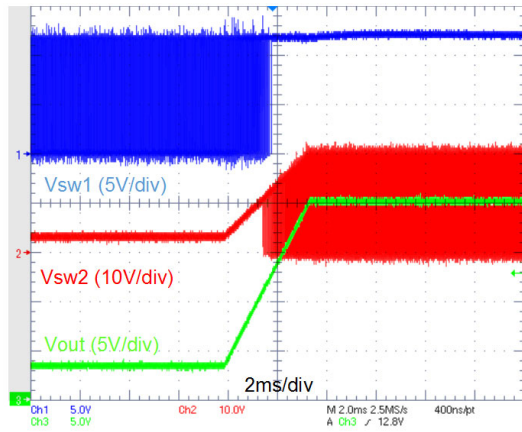
VIN=12V, VOUT=5~20V

**Figure 13. Voltage Ramp Up**  
(slew rate = 0.6 V/ms)



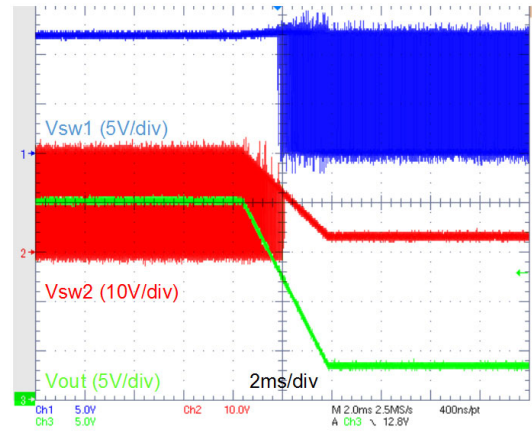
VIN=12V, VOUT=20~5V

**Figure 14. Voltage Ramp Down**  
(slew rate = 0.6 V/ms)



VIN=12V, VOUT=5~20V

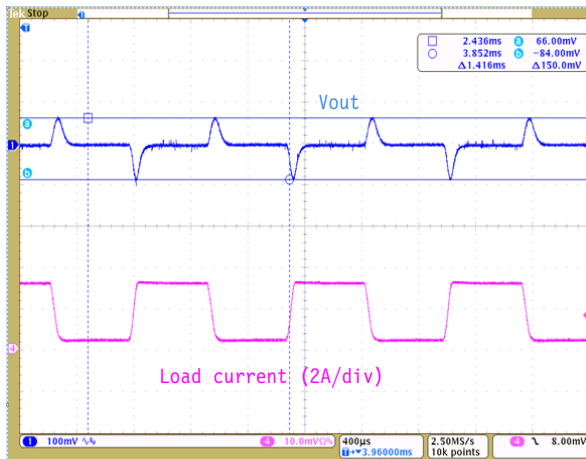
**Figure 15. Voltage Ramp Up**  
(slew rate = 4.8 V/ms)



VIN=12V, VOUT=20~5V

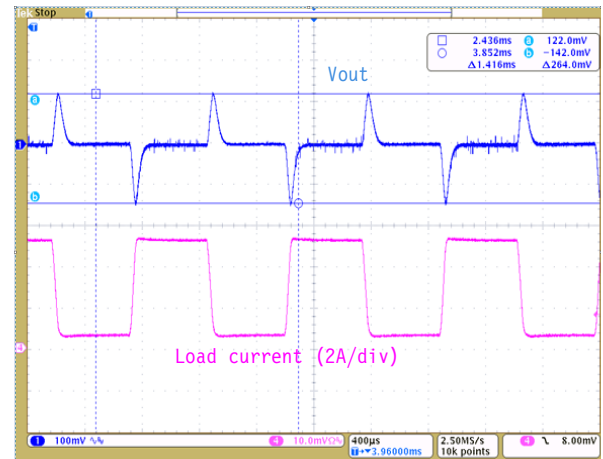
**Figure 16. Voltage Ramp Down**  
(slew rate = 4.8 V/ms)

TYPICAL CHARACTERISTICS



Vin=24V, Vout=5V, Load=0.3A to 3A

Figure 17. 5 V Load Step



Vin=24V, Vout=5V, Load=0.5A to 5A

Figure 18. 20 V Load Step

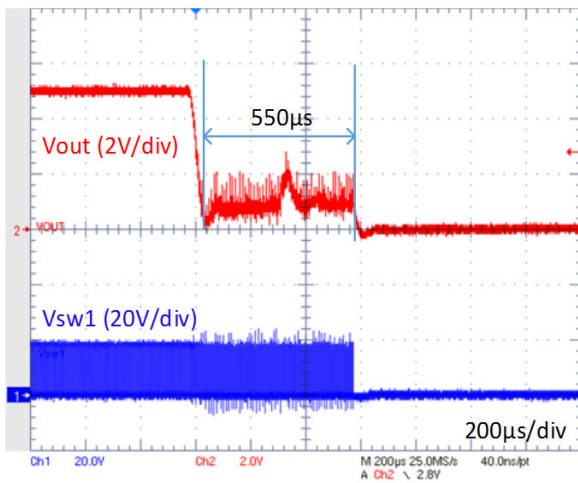


Figure 19. OCP Cycle-by-Cycle Waveform

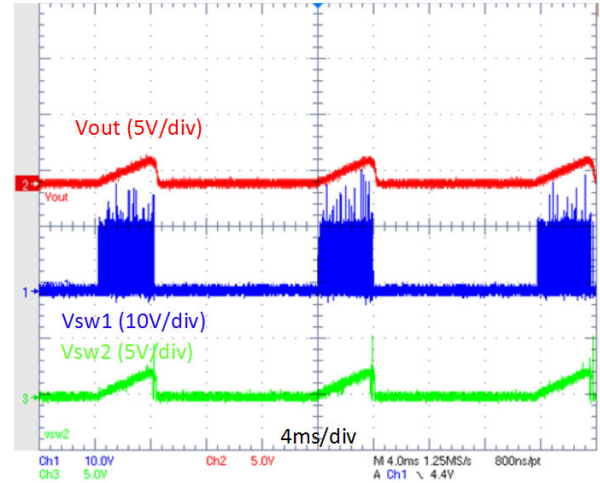


Figure 20. OCP Hiccup Waveform

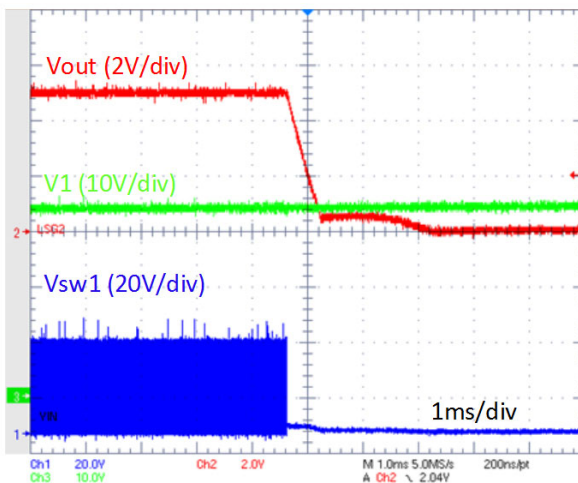


Figure 21. OVP Waveform

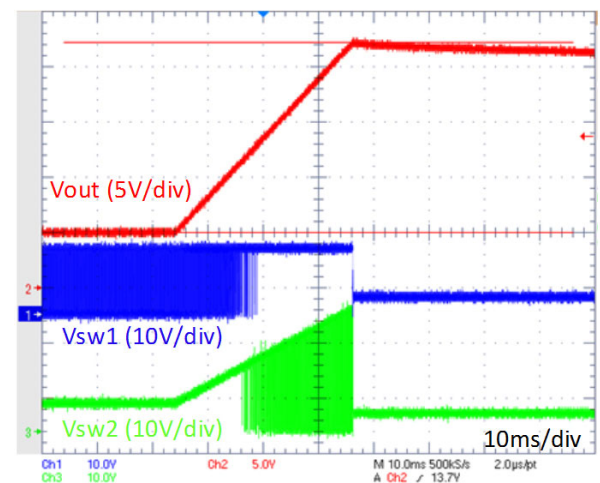
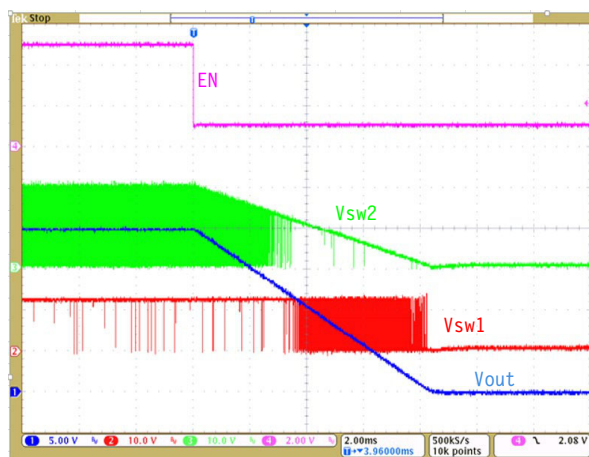


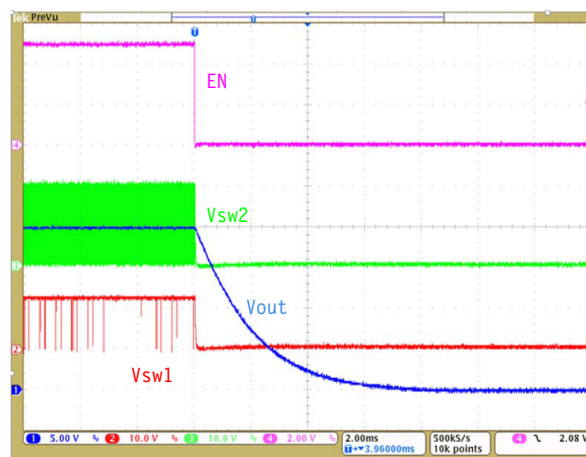
Figure 22. V2 Secondary OVP Waveform

TYPICAL CHARACTERISTICS



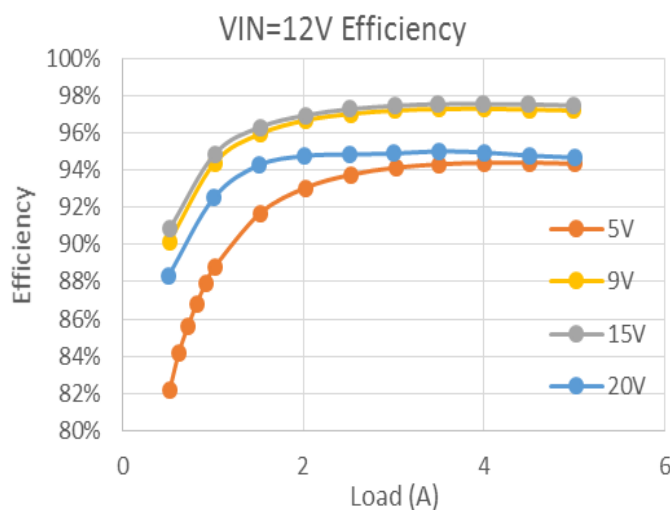
Vin=12V, Vout=20V

**Figure 23. Shutdown by EN**  
Vout gradually walks down, after EN pin goes down from high (5V) to middle (1V)



Vin=12V, Vout=20V

**Figure 24. Shutdown by EN**  
Vout is discharged by load current, after EN pin does down from high (5V) to low (0V)



**Figure 25. Efficiency vs. Load (MOSFET part number is NTMFS4C10N)**

## APPLICATION INFORMATION

### Dual Edge Current Mode Control

When dual edge current mode control is used, two voltage ramps are generated that are 180 degrees out of phase. The inductor current signal is added to the ramps to incorporate current mode control. In Figure 26, the COMP signal from the compensation output interacts with two triangle ramps to generate gate signals to the switches from S1 to S4. Two ramp signals cross twice at midpoint within a cycle. When COMP is above the midpoint, the system will operate at

boost mode with S1 always on and S2 always off, but S3 and S4 turning on alternatively in an active switching mode. When COMP is below the midpoint, the system will operate at buck mode, with S4 always on and S3 always off, but S1 and S2 turning on alternatively in an active switching mode. The controller can switch between buck and boost mode smoothly based on the COMP signal from peak current regulation.

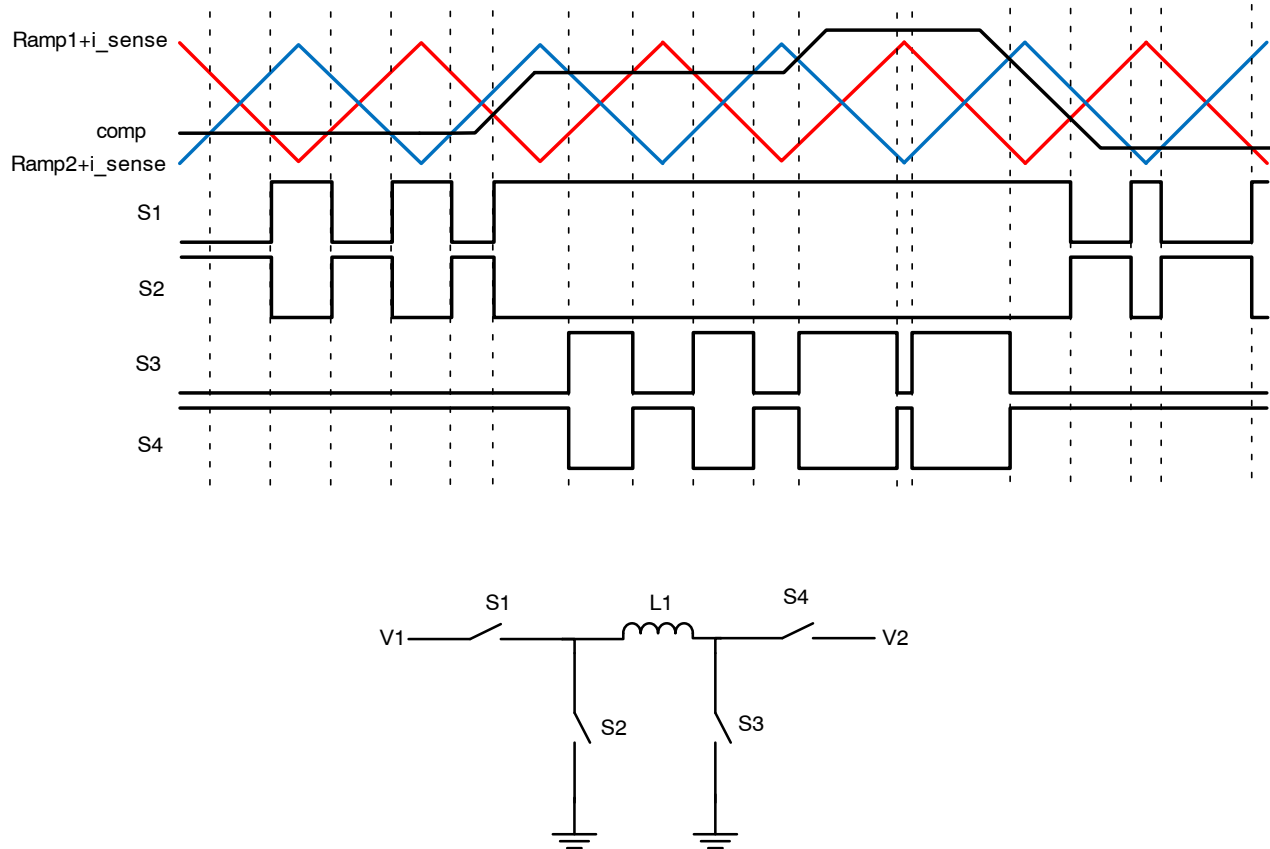


Figure 26. Transitions for Dual Edge 4 Switch Buck Boost

### Feedback and Output Voltage Profile

The feedback of the converter output voltage is connected to the FB pin of the device through a resistor divider. Internally FB is connected to the inverting input of the internal transconductance error amplifier. The non-inverting input of the gm amplifier is connected to the internal reference. The internal reference voltage is by default 0.5 V. Therefore a 10:1 resistor divider from the converter output to the FB will set the output voltage to 5 V

in default. The reference voltage can be adjusted with 10 mV (default) or 5 mV steps from 0.1 V to 2.55 V through the voltage profile register (01H), which makes the continuous output voltage profile possible through an external resistor divider. For example, by default, if the external resistor divider has a 10:1 ratio, the output voltage profile will be able to vary from 1 V to 25.5 V with 100 mV steps.

**Table 4. VOLTAGE PROFILE REGISTER SETTINGS**

| dac_target (01h) |       |       |       |       |       |       |       | dac_target (01h)<br>Hex Value | dac_target lsb<br>(03h, bit 4) | Reference DAC<br>Voltage (mV) |
|------------------|-------|-------|-------|-------|-------|-------|-------|-------------------------------|--------------------------------|-------------------------------|
| bit_8            | bit_7 | bit_6 | bit_5 | bit_4 | bit_3 | bit_2 | bit_1 |                               | bit_0                          |                               |
| 0                | 0     | 0     | 0     | 0     | 0     | 0     | 0     | 00                            | 1                              | 5                             |
| ...              | ...   | ...   | ...   | ...   | ...   | ...   | ...   | ...                           | ...                            | ...                           |
| 0                | 0     | 1     | 0     | 0     | 0     | 0     | 1     | 21                            | 0                              | 330                           |
| 0                | 0     | 1     | 0     | 0     | 0     | 0     | 1     | 21                            | 1                              | 335                           |
| ...              | ...   | ...   | ...   | ...   | ...   | ...   | ...   | ...                           | ...                            | ...                           |
| 0                | 0     | 1     | 1     | 0     | 0     | 1     | 0     | 32                            | 0                              | 500 (Default)                 |
| ...              | ...   | ...   | ...   | ...   | ...   | ...   | ...   | ...                           | ...                            | ...                           |
| 1                | 1     | 0     | 0     | 1     | 0     | 0     | 0     | C8                            | 0                              | 2000                          |
| ...              | ...   | ...   | ...   | ...   | ...   | ...   | ...   | ...                           | ...                            | ...                           |
| 1                | 1     | 1     | 1     | 1     | 1     | 1     | 1     | FF                            | 0                              | 2550                          |
| 1                | 1     | 1     | 1     | 1     | 1     | 1     | 1     | FF                            | 1                              | 2555                          |

### Transconductance Voltage Error Amplifier

To maintain loop stability under a large change in capacitance, the NCV81599 can change the gm of the internal transconductance error amplifier from 87  $\mu$ S to

1000  $\mu$ S allowing the DC gain of the system to be increased more than a decade triggered by the adding and removal of the bulk capacitance or in response to another user input. The default transconductance is 500  $\mu$ S.

**Table 5. AVAILABLE TRANSCONDUCTANCE SETTING**

| Address        | AMP_2 | AMP_1 | AMP_0 | Amplifier GM Value ( $\mu$ S) |
|----------------|-------|-------|-------|-------------------------------|
| 07h, bit [2:0] | 0     | 0     | 0     | 87                            |
|                | 0     | 0     | 1     | 100                           |
|                | 0     | 1     | 0     | 117                           |
|                | 0     | 1     | 1     | 333                           |
|                | 1     | 0     | 0     | 400                           |
|                | 1     | 0     | 1     | 500 (default)                 |
|                | 1     | 1     | 0     | 667                           |
|                | 1     | 1     | 1     | 1000                          |

### Programmable Slew Rate

The slew rate of the NCV81599 is controlled via the I<sup>2</sup>C registers with the default slew rate set to 0.6 mV/ $\mu$ s (FB = 0.1 V<sub>2</sub>, assume the resistor divider ratio is 10:1) which is the slowest allowable rate change. The slew rate is used when the output voltage starts from 0 V to a user selected profile level, changing from one profile to another, or when the output voltage is dynamically changed. The

output voltage is divided by a factor of the external resistor divider and connected to FB pin. The 9 Bit DAC is used to increase the reference voltage in 10 or 5 mV increments. The slew rate is decreased by using a slower clock that results in a longer time between voltage steps, and conversely increases by using a faster clock. The step monotonicity depends on the bandwidth of the converter where a low

bandwidth will result in a slower slew rate than the selected value. The available slew rates are shown in Table 6. The selected slew rate is maintained unless the current limit is

tripped; in which case the increased voltage will be governed by the positive current limit until the output voltage falls or the fault is cleared.

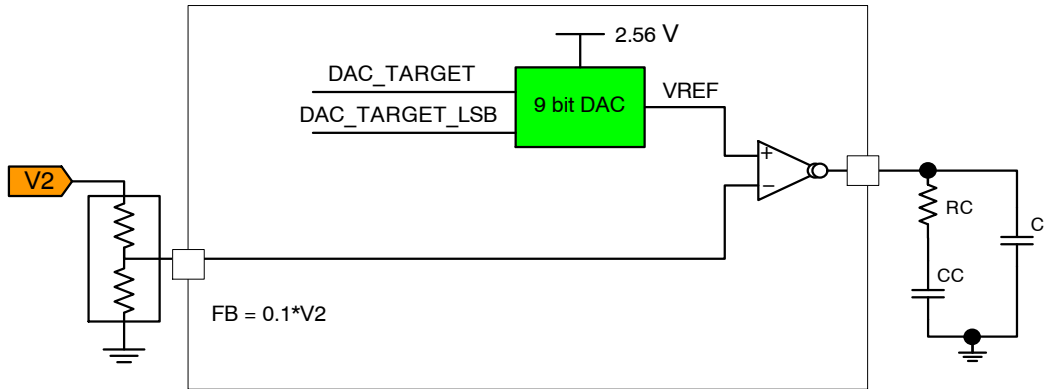


Figure 27. Slew Rate Limiting Block Diagram and Waveforms

Table 6. SLEW RATE SELECTION

| Address        | Slew Bits | Soft Start or Voltage Transition (FB = 0.1*V2) |
|----------------|-----------|------------------------------------------------|
| 02h, bit [1:0] | Slew_0    | 0.6 mV/μs                                      |
|                | Slew_1    | 1.2 mV/μs                                      |
|                | Slew_2    | 2.4 mV/μs                                      |
|                | Slew_3    | 4.8 mV/μs                                      |

The discharge slew rate is accomplished in much the same way as the charging except the reference voltage is decreased rather than increased. The slew rate is maintained unless the negative current limit is reached. If the negative current limit is reached, the output voltage is decreased at the maximum rate allowed by the current limit (see the negative current limit section).

#### Soft-Start and EN Pin

During a 0 V soft-start, standard converters can start in synchronous mode and have a monotonic rising of output voltage. If a prebias exists on the output and the converter starts in synchronous mode, the prebias voltage could be discharged. The NCV81599 controller ensures that if a prebias is detected, the soft-start is completed in a non-synchronous mode to prevent the output from discharging. During soft-start, the output rising slew rate will follow the slew rate register with default value set to 0.6 mV/μs (FB = 0.1\*V2).

The EN Pin has 2 levels of threshold: the internal LDO and I<sup>2</sup>C function are powered up when EN pin reaches ~0.8 V; while the buck-boost conversion starts when EN pin reaches

~2.0 V. The EN pin can NOT work with very slow dv/dt signals. Please always keep the EN pin input signal faster than 0.5 V/ms. The EN pin has a pull-up current of ~3 μA, so that an open EN pin powers up the NCV81599. To keep the EN pin signal faster enough, please keep total capacitance on the EN pin below 4.7 nF.

When the EN pin goes from high (above ENHT) down to middle (below ENLT, but still above ENLDOHT), the NCV81599 walks down the Vout gradually to zero, in the discharge slew rate selected by “voltage transition slew rate” register value, as shown in waveforms in Figure 23. All the I<sup>2</sup>C register value stays.

When the EN pin goes from high (above ENHT) down to low (below ENLDOLT), the NCV81599 stops all switching immediately, and Vout is discharged by load current, as shown in waveforms in Figure 24. Internal LDO shuts down, and all I<sup>2</sup>C register value resets.

#### Frequency Programming

The switching frequency of the NCV81599 can be programmed from 150 kHz to 1.2 MHz via the I<sup>2</sup>C interface. The default switching frequency is set to 600 kHz. The switching frequency can be changed on the fly. However, it is a good practice to disable the part and then program to a different frequency to avoid transition glitches at large load current.

The NVP81599 employs a minimum switching frequency circuit (F<sub>MIN</sub>) to ensure the bootstrap caps remain charged and operation in the audible hearing range band is avoided. Typically, this circuit is only active when V<sub>IN</sub> is near V<sub>OUT</sub> at light loads.

Table 7. FREQUENCY PROGRAMMING TABLE

| Name  | Bit       | Definition        | Description                                                                                                                                                                                                     |
|-------|-----------|-------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Freq1 | 03H [2:0] | Frequency Setting | 3 Bits that Control the Switching Frequency from 150 kHz to 1.2 MHz.<br>000: 600 kHz (default)<br>001: 150 kHz<br>010: 300 kHz<br>011: 450 kHz<br>100: 750 kHz<br>101: 900 kHz<br>110: 1.2 MHz<br>111: Reserved |

### Current Sense Amplifiers

Internal precision differential amplifiers measure the potential between the terminal CSP1 and CSN1 or CSP2 and CSN2. Current flows from the input V1 to the output in a buck boost design. Current flowing from V1 through the switches to the inductor passes through  $R_{SENSE}$ . The external sense resistor,  $R_{SENSE}$ , has a significant effect on the function of current sensing and limiting systems and must be chosen with care. First, the power dissipation in the resistor should be considered. The system load current will cause both heat and voltage loss in  $R_{SENSE}$ . The power loss and voltage drop drive the designer to make the sense resistor as small as possible while still providing the input dynamic range required by the measurement. Note that input dynamic range is the difference between the maximum input signal and the minimum accurately measured signal, and is limited primarily by input DC offset of the internal

amplifier. In addition,  $R_{SENSE}$  must be small enough that  $V_{SENSE}$  does not exceed the maximum input voltage 100 mV, even under peak load conditions.

The potential difference between  $CSP_x$  and  $CSN_x$  is level shifted from the high voltage domain to the low voltage  $VCC$  domain where the signal is split into two paths.

The first path, or external path, allows the end user to observe the analog or digital output of the high side current sense. The external path gain is set by the end user allowing the designer to control the observable voltage level. The voltage at CS1 or CS2 can be converted to 7 bits by the ADC and stored in the internal registers which are accessed through the I<sup>2</sup>C interface.

The second path, or internal path, has internally set gain of 10 and allows cycle by cycle precise limiting of positive and negative peak input current limits.

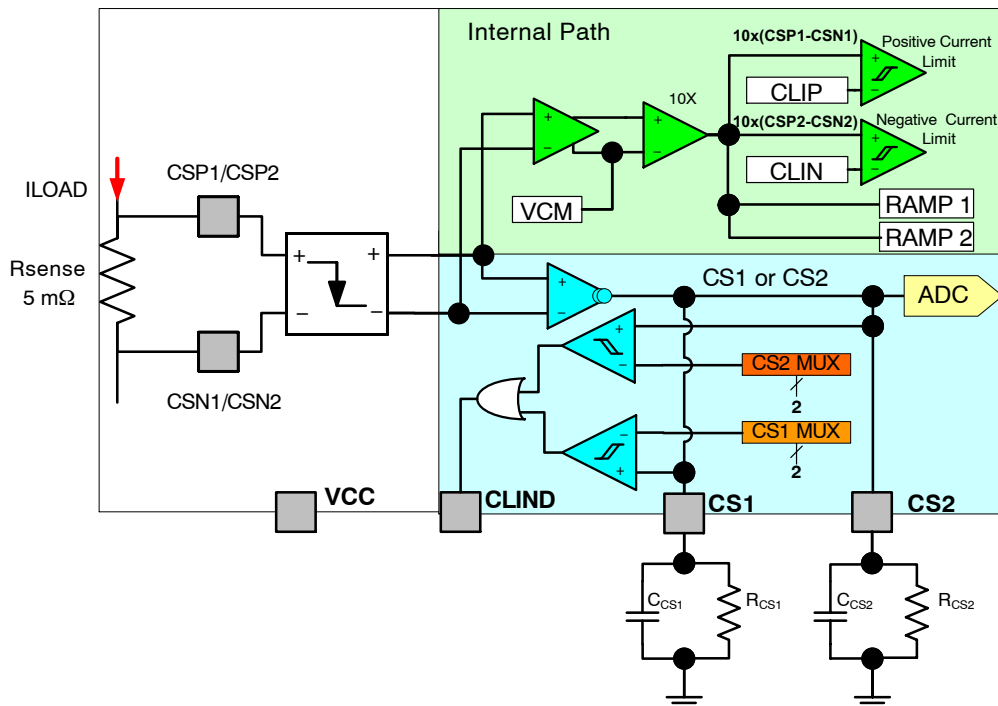


Figure 28. Block Diagram and Typical Connection for Current Sense

### Positive Current Limit Internal Path

The NCV81599 has a pulse by pulse current limiting function activated when a positive current limit triggers. CSP1/CSN1 will be the positive current limit sense channel.

When a positive current limit is triggered, the current pulse is truncated. In both buck mode and in boost mode the S1 switch is turned off to limit the energy during an over current event. The current limit is reset every switching cycle and waits for the next positive current limit trigger. In this way, current is limited on a pulse by pulse basis. Pulse by pulse current limiting is advantageous for limiting energy

into a load in over current situations but are not up to the task of limiting energy into a low impedance short. To address the low impedance short, the NCV81599 does pulse by pulse current limiting for 500  $\mu$ s known as Ilim timeout, the controller will enter into hiccup mode. The NCV81599 remains in fast stop state with all switches driven off for 10 ms. Once the 10 ms has expired, the part is allowed to soft start to the previously programmed voltage and current level if the short circuit condition is cleared.

The internal current limits can be controlled via the I<sup>2</sup>C interface as shown in Table 8.

**Table 8. INTERNAL PEAK CURRENT LIMIT**

| CLIN_1 | CLIN_0 | Address       | CSP2-CSN2 (mV) | Current at RSENSE = 5 m $\Omega$ (A) |
|--------|--------|---------------|----------------|--------------------------------------|
| 0      | 0      | 05h, bit[5:4] | -40 (Default)  | -8                                   |
| 0      | 1      |               | -25            | -5                                   |
| 1      | 0      |               | -15            | -3                                   |
| 1      | 1      |               | 0              | 0                                    |
| CLIP_1 | CLIP_0 | Address       | CSP1-CSN1 (mV) | Current at RSENSE = 5 m $\Omega$ (A) |
| 0      | 0      | 05h, bit[1:0] | 38 (Default)   | 7.6                                  |
| 0      | 1      |               | 23             | 4.6                                  |
| 1      | 0      |               | 11             | 2.2                                  |
| 1      | 1      |               | 70             | 14                                   |

### Positive Current Limit Internal Latch-off

In addition to the positive current limit, there is a latch-off over current protection, to provide quick protection against output short and inductor saturation. The latch-off over current protection, OCP\_L, sensed across CSP2-CSN2

pins, has its threshold around twice that of the positive current limit. As listed in the following table, OCP\_L threshold is set by the same I<sup>2</sup>C register bits, CLIP\_1 and CLIP\_0, which set the internal positive peak current limit at the same time.

**Table 9. THE LATCH-OFF CURRENT LIMIT OCP\_L**

| CLIP_1 | CLIP_0 | Address       | CSP2-CSN2 (mV) | Current at RSENSE = 5 m $\Omega$ (A) |
|--------|--------|---------------|----------------|--------------------------------------|
| 0      | 0      | 05h, bit[1:0] | 70 (Default)   | 14                                   |
| 0      | 1      |               | 38             | 7.6                                  |
| 1      | 0      |               | 23             | 4.6                                  |
| 1      | 1      |               | 106            | 21.2                                 |

Once the latch-off current limit protection is triggered, an input OCP\_L fault is set. All four switches are driven off immediately. The OCP\_L interrupt register bit set to 1. Only toggling the EN or input power recycle can reset the part. The latch-off current limit OCP\_L can be disabled via I<sup>2</sup>C register as shown in the following table.

**Table 10. OCP\_L LATCH-OFF CURRENT LIMIT ENABLING AND DISABLING**

| Address     | Dis_OCP_L | Description           |
|-------------|-----------|-----------------------|
| 04h, bit[1] | 0         | OCP_L Action Enabled  |
| 04h, bit[1] | 1         | OCP_L Action Disabled |

### Negative Current Limit Internal Path

Negative current limit can be activated in a few instances, including light load synchronous operation, heavy load to

light load transition, output overvoltage, and high output voltage to lower output voltage transitions. CSP2/CSN2 will be the negative current limit sense channel.

During light load synchronous operation, or heavy load to light load transitions the negative current limit can be triggered during normal operation. When the sensed current exceeds the negative current limit, the S4 switch is shut off preventing the discharge of the output voltage both in buck mode and in boost mode if the output is in the power good range. Both in boost mode and in buck mode when a negative current is sensed, the S4 switch is turned off for the remainder of either the S4 or S2 switching cycle and is turned on again at the appropriate time. In buck mode, S4 is turned off at the negative current limit transition and turned on again as soon as the S2 on switch cycle ends. In boost mode, the S4 switch is the rectifying switch and upon

negative current limit the switch will shut off for the remainder of its switching cycle. The internal negative current limits can be controlled via the I<sup>2</sup>C interface as shown in Table 8.

#### External Path (CS1, CS2, CLIND)

The voltage drop across the sense resistors as a result of the load can be observed on the CS1 and CS2 pins. Both CS1, CS2 can be monitored with a high impedance input. The voltage drop is converted into a current by a transconductance amplifier with a typical GM of 5 mS. The final gain of the output is determined by the end users selection of the R<sub>CS</sub> resistors. The output voltage of the CS pin can be calculated from Equation 1. The user must be careful to keep the dynamic range below 2.56 V when considering the maximum short circuit current.

$$V_{CS} = (I_{AVERAGE} * R_{SENSE} * Trans) * R_{CS} < 2.56 V \Rightarrow$$

$$R_{CS} = \frac{V_{CS}}{I_{AVERAGE} * R_{SENSE} * Trans} < \frac{2.56 V}{I_{MAX} * R_{SENSE} * Trans}$$

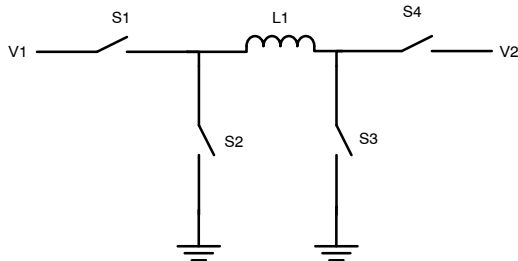
(eq. 1)

**Table 11. REGISTER SETTING FOR THE CLIM COMPARATORS**

| Address        | CLIMx_1 | CLIMx_0 | CSx_LIM (V) | Current at RSENSE = 5 mΩ<br>RSET = 20 kΩ (A) | Current at RSENSE = 5 mΩ<br>RSET = 10 kΩ (A) |
|----------------|---------|---------|-------------|----------------------------------------------|----------------------------------------------|
| 06h, bit [3:0] | 0       | 0       | 0.25        | .5                                           | 1                                            |
|                | 0       | 1       | 0.75        | 1.5                                          | 3                                            |
|                | 1       | 0       | 1.5         | 3                                            | 6                                            |
|                | 1       | 1       | 2.5         | 5                                            | 10                                           |

#### Overvoltage Protection (OVP)

When the divided output voltage is 15% (typical) above the internal reference voltage for greater than one switching cycle, an OV fault is set. During an overvoltage fault, S1 is driven off, S2 is driven on, and S3 and S4 are modulated to discharge the output while preventing the inductor current from going beyond the I<sup>2</sup>C programmed negative current limit.

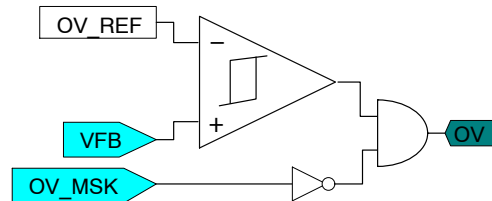


**Figure 29. Diagram for OV Protection**

During overvoltage fault detection the switching frequency changes from its I<sup>2</sup>C set value to 50 kHz to reduce the power dissipation in the switches and prevent the inductor from saturating. OVP is disabled during voltage changes to ensure voltage changes and glitches during slewing are not falsely reported as faults. The OVP faults are reengaged 2 ms after completion of the soft start.

The speed and accuracy of the dual amplifier stage allows the reconstruction of the input and output current signal, creating the ability to limit the peak current. If the user would like to limit the mean DC current of the switch, a capacitor can be placed in parallel with the R<sub>CS</sub> resistors. CS1, CS2 can be monitored with a high impedance input.

CS1, CS2 voltages are connected internally to 2 high speed low offset comparators. When the external CLIND flag is triggered, i.e., CLIND pin voltage is pulled high, it indicates that one of the internal comparators has exceeded the preset limit (CSx\_LIM). The default comparator setting is 250 mV which is a limit of 500 mA with a current sense resistor of 5 mΩ and an R<sub>CS</sub> resistor of 20 kΩ. The external current limit settings are shown in Table 11.



**Figure 30. OV Block Diagram**

#### Input Overvoltage Lockout (OVLO) Protection

The goal of the input OVLO fault detection is to protect our IC from overvoltage damage and obtain regulation again once the OVLO fault is cleared. OVLO can be a latched shutdown or hiccup mode by a user register.

In a latched shutdown mode, when the input voltage is higher than V<sub>OVLOIN\_R</sub> for greater than the debounce time, an input OVLO fault is set. All switches are driven off immediately. The PG and input OVLO interrupt registers are set to 1. Only toggling the EN or input power recycle can reset the part.

In a hiccup mode, when the input voltage is higher than V<sub>OVLOIN\_R</sub> for greater than the debounce time, an input OVLO fault is set. The OVLO debounce time is to filter any overvoltage spike that is shorter than the time. During an input OV fault, all switches are driven off immediately. The

DAC voltage is reset to 0. The PG and input OVLO interrupt registers are set to 1. Once the input voltage falls under the threshold, the debounce time starts counting. If input OVLO keeps not detected during the OVLO recover debounce time, a soft start will be reengaged.

Input OVLO detection starts from the beginning of soft-start and ends in shutdown.

### Output OVLO Protection and V2 Pin

The goal of the output OVLO fault detection is to protect the MOSFET from overvoltage damage. The overvoltage can be created by accidentally write a wrong number in the DAC\_target register or installation problem on the external feedback voltage divider. The default output OVLO threshold is 30V. Customer can write to the 2-bit output OVLO register 06h bit[5:4], sel\_ov2th to configure the threshold.

The output OVLO threshold can be set as 15V, 22.5V, 30V and 36V, therefore it can be used for customer user cases that requires a max output voltage of 10V, 15V, 20V and 25.5V, respectively. Since most of the time, OVP should be able to protect the output over voltage, the output OVLO threshold are set >40% higher than the max output in that range. When the output has run away due to either external voltage divider or DAC configure error, output OVLO will kick into action.

Output OVLO has a latched shutdown mode. When the output voltage is higher than the output OVLO threshold for greater than the debounce time, an OVLO fault is set. The output OVLO interrupt register will be set to 1. All switches are driven off immediately. The PG and output OVLO interrupt registers are set to 1. Toggling the EN or input power recycle can reset the part.

Output OVLO detection starts from the beginning of soft-start and ends in shutdown.

The output OVLO is sensed on the V2 pin. In some extreme conditions, the V2 pin voltage, i.e. the output voltage, may be pulled to negative, such as when the output is short by a long cable. When V2 pin voltage goes negative, the NCV81599 may enter a VCC UVLO, which resets all registers to default and initial a soft-start. To prevent negative voltage on V2 pin, a resistor, such as 1 k $\Omega$ , can be placed between V2 pin and output voltage.

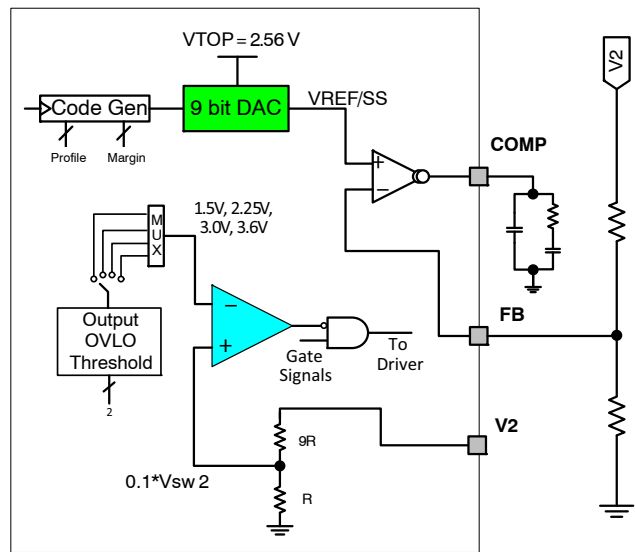


Figure 31. Output OVLO

### Power Good Monitor (PG)

NCV81599 provides two window comparators to monitor the internal feedback voltage. The target voltage window is  $\pm 5\%$  of the reference voltage (typical). Once the feedback voltage is within the power good window, a power good indication is asserted once a 3.3 ms timer has expired. If the feedback voltage falls outside a  $\pm 7.5\%$  window for greater than 1 switching cycle, the power good register is reset. Power good is indicated on the INT pin if the I<sup>2</sup>C register is set to display the PG state. When DAC is set to below 400 mV, the PG high threshold is kept at a constant voltage, and the PG low threshold is kept at 0 to avoid false triggering.

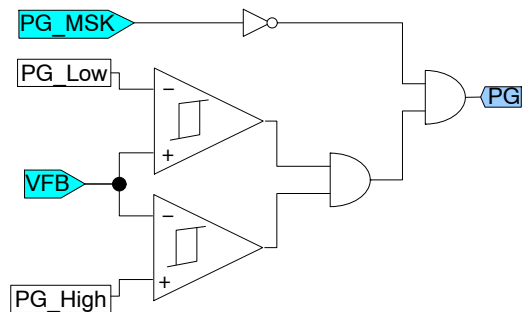


Figure 32. PG Block Diagram

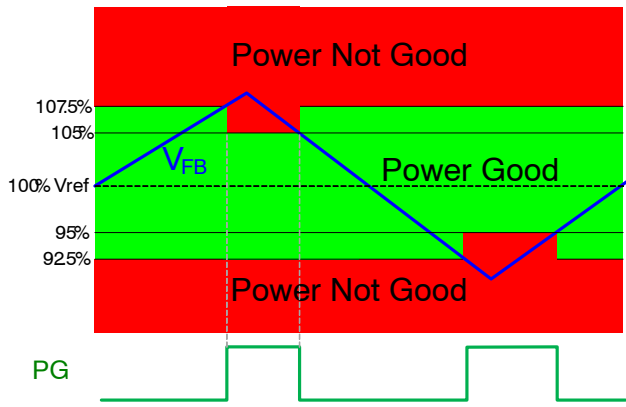


Figure 33. Power Good Diagram

### Thermal Shutdown

The NCV81599 protects itself from overheating with an internal thermal shutdown circuit. If the junction temperature exceeds the thermal shutdown threshold (typically 150°C), all MOSFETs will be driven to the off state, and the part will wait until the temperature decreases to an acceptable level. The fault will be reported to the fault register and the INT flag will be set unless it is masked. When the junction temperature drops below 125°C (typical), the part will discharge the output voltage to Vsafe 0 V.

### PFET Drive

The PMOS drive is an open drain output used to control the turn on and turn off of PMOSFET switches at a floating potential. The external PMOS can be used as a cutoff switch, enable for an auxiliary power supply, or a bypass switch for a power supply. The RDSon of the pulldown NMOSFET is typically 20 Ω allowing the user to quickly turn on large PMOSFET power channels.

Table 12. PFET ACTIVATION TABLE

| Address      | PFET_DRV | Description        |
|--------------|----------|--------------------|
| 04h, bit [0] | 0        | NFET OFF (Default) |
|              | 1        | NFET ON            |

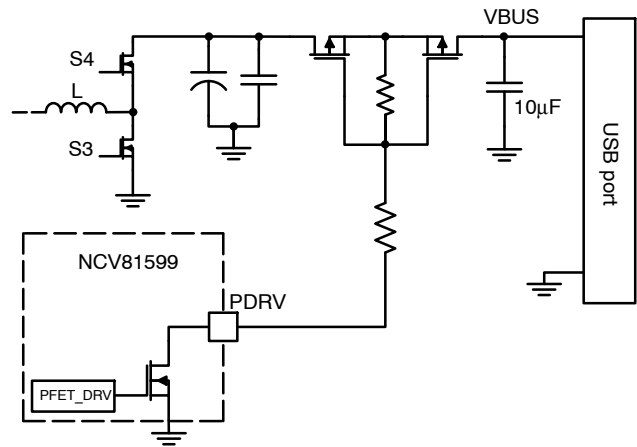


Figure 34. PFET Drive

### Analog to Digital Converter

The analog to digital converter is a 7-bit A/D which can be used as an event recorder, an input voltage sampler, output voltage sampler, input current sampler, or output current sampler. The converter digitizes real time data during the sample period. The internal precision reference is used to provide the full range voltage; in the case of V1(input voltage), or FB (with 10:1 external resistor divider) the full range is 0 V to 25.5 V. The V1 is internally divided down by 10 before it is digitized by the ADC, thus the range of the measurement is 0 V–2.55 V, same as FB. The resolution of the V1 and FB voltage is 20 mV at the analog mux, but since the voltage is divided by 10 output voltage resolution will be 200 mV. Therefore, the highest input voltage report is 200 mV x 127 = 25.4 V. When CS1 and CS2 are sampled, the range is 0 V–2.55 V. The resolution will be 20 mV in the CS monitoring case. The actual current can be calculated by dividing the CS1 or CS2 values with the factor of Rsense × 5 mS × RCSx, the total gain from the current input to the external current monitoring outputs.

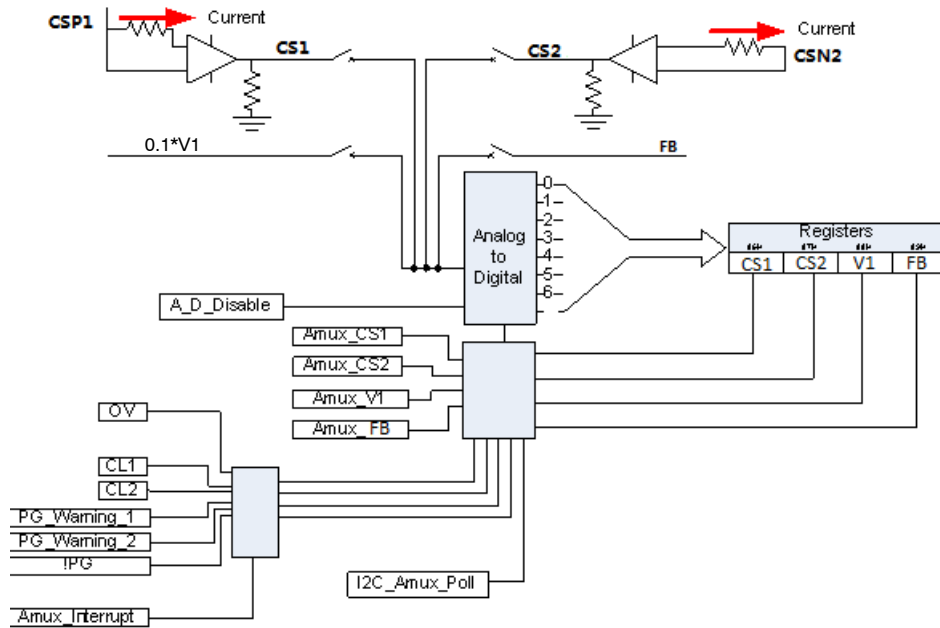


Figure 35. Analog to Digital Converter

Table 13. ADC RESULT BYTE

| Address            | MSB | 5  | 4  | 3  | 2  | 1  | LSB |
|--------------------|-----|----|----|----|----|----|-----|
| 10h, 11h, 12h, 13h | D6  | D5 | D4 | D3 | D2 | D1 | D0  |

Table 14. REGISTER SETTING FOR ENABLING DESIRED ADC BEHAVIOUR

| Address        | ADC_2 | ADC_1 | ADC_0 | Description                                                   |
|----------------|-------|-------|-------|---------------------------------------------------------------|
| 08h, bit [4:2] | 0     | 0     | 0     | Set Amux to VFB                                               |
|                | 0     | 0     | 1     | Sets Amux to V1                                               |
|                | 0     | 1     | 0     | Set Amux to CS2                                               |
|                | 0     | 1     | 1     | Set Amux to CS1                                               |
|                | 1     | 0     | 0     | Select all in rotating sequence (VFB, V1, CS2, CS1, VFB, ...) |

Table 15. REGISTER SETTING FOR ADC TRIGGER MANNER

| Address        | ADC Trigger | Description                                      |
|----------------|-------------|--------------------------------------------------|
| 08h, bit [1:0] | 00          | Trigger a 1x read by a fault condition (Default) |
|                | 01          | Trigger a 1x read                                |
|                | 10          | Trigger a continuous read                        |

### Interrupt Control

The interrupt controller continuously monitors internal interrupt sources, generating an interrupt signal when a system status change is detected. Individual bits generating interrupts will be set to 1 in the INTACK register (I<sup>2</sup>C read only registers), indicating the interrupt source. INTACK register is automatically reset by an I<sup>2</sup>C read. All interrupt sources can be masked by writing 1 in register INTMSK of

09h and 0Ah. Masked sources will never generate an interrupt request on the INT pin. The INT pin is an open drain output. A non-masked interrupt request will result in the INT pin being driven high. When the host reads the INTACK registers, the INT pin will be driven low and the interrupt register INTACK is cleared. Figure 36 illustrates the interrupt process.

## NCV81599, NCP81599

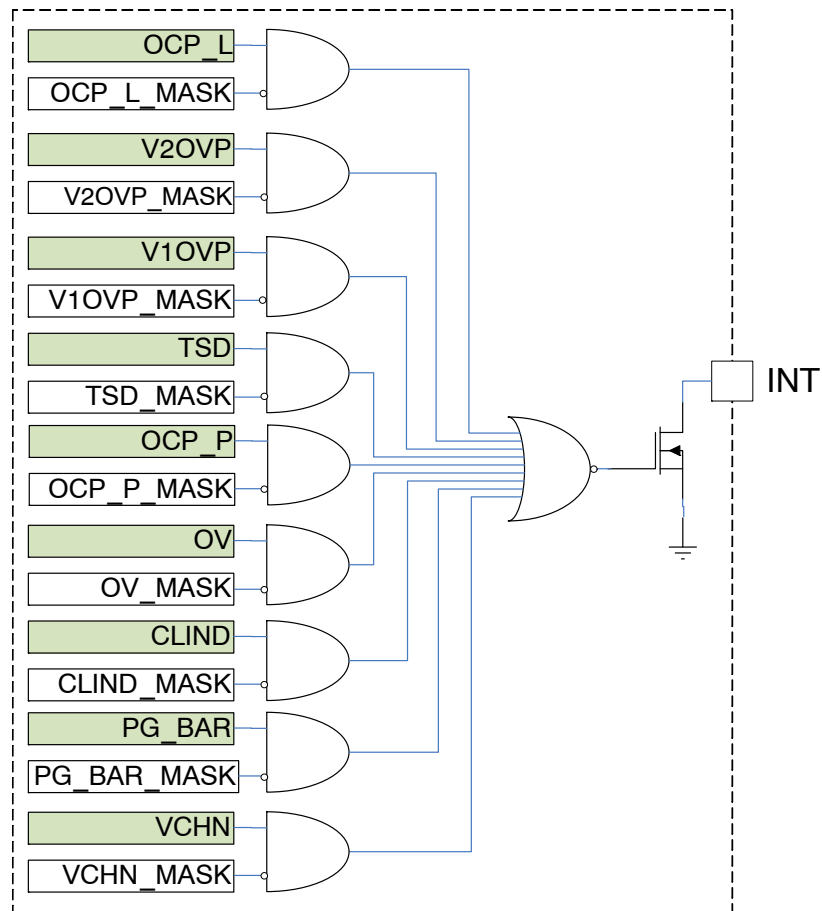


Figure 36. Interrupt Logic

Table 16. INTERPRETATION TABLE

| Interrupt Name | Register name | Address      | Description                              |
|----------------|---------------|--------------|------------------------------------------|
| OCP_L          | ocp_l         | 14h, bit [6] | Internal positive over current latch-off |
| V2OVP          | v2ovp         | 14h, bit [5] | Output secondary over voltage            |
| V1OVP          | v1ovp         | 14h, bit [4] | Input over voltage                       |
| TSD            | tsd           | 14h, bit [3] | Thermal shut down                        |
| OCP_P          | ocp_p         | 14h, bit [2] | Internal positive over current           |
| OV             | ov            | 14h, bit [1] | Output over voltage                      |
| CLIND          | ext_clind_ocp | 14h, bit [0] | External over current trip from CLIND    |
| VCHN           | vchn          | 15h, bit [1] | Output negative voltage change           |
| PG_BAR         | pg_int        | 15h, bit [0] | Power good bar thresholds exceeded       |

### I<sup>2</sup>C Address and Registers

NCV81599 can set up to 4 different I<sup>2</sup>C addresses by sensing the shunt resistor voltage at ADDR pin. The chip will source a 10  $\mu$ A current to the ADDR resistor and sense the voltage corresponding to different I<sup>2</sup>C addresses everytime when it is powered on. Suggest to put resistors of

0  $\Omega$ , 26.1 k $\Omega$ , 44.2 k $\Omega$ , 71.5 k $\Omega$  from ADDR pin to GND to set I<sup>2</sup>C address 74H, 75H, 76H, 77H respectively.

Unused bits in the register map below are marked with “-”. Writing either “1” or “0” into these unused bits in user-programmable registers does NOT change any function/performance of the NCV81599.

Table 17. I2C REGISTER MAP BIT DETAIL

|                             | ADDR<br>(Hex) | Bit 7      | Bit 6          | Bit 5          | Bit 4          | Bit 3        | Bit 2          | Bit 1         | Bit 0          | Default |
|-----------------------------|---------------|------------|----------------|----------------|----------------|--------------|----------------|---------------|----------------|---------|
| User-programmable Registers | 00h           | –          | –              | 0              | 0              | en_int       | en_mask        | –             | –              | 00h     |
|                             | 01h           | dac_target |                |                |                |              |                |               |                | 32h     |
|                             | 02h           | –          | –              | –              | –              | –            | –              | slew_rate     |                | 00h     |
|                             | 03h           | –          | –              | v1ovp_lat      | dac_target_isb | –            | pwm_frequency  |               |                | 00h     |
|                             | 04h           | –          | –              | cs2_dchrg      | cs1_dchrg      | –            | –              | dis_ocr_l     | pfet           | 00h     |
|                             | 05h           | –          | –              | ocr_clim_neg   |                | –            | –              | ocr_clim_pos  |                | 00h     |
|                             | 06h           | –          | –              | sel_ov2th      |                | cs2_clim_pos |                | cs1_clim_pos  |                | 20h     |
|                             | 07h           | –          | –              | –              | –              | –            | gm_amp_setting |               |                | 05h     |
|                             | 08h           | –          | –              | dis_adc        | amux_sel       |              |                | amux_trigger  |                | 00h     |
|                             | 09h           | –          | int_mask_ocr_l | int_mask_v2ovp | int_mask_v1ovp | int_mask_tsd | int_mask_ocr_p | int_mask_ov   | int_mask_clind | 00h     |
|                             | 0Ah           | –          | –              | –              | –              | –            | –              | int_mask_vchn | int_mask_pg    | 00h     |
| –                           | 0B .. 0Fh     |            |                |                |                |              |                |               |                |         |
| User Read-only Registers    | 10h           | –          | vfb            |                |                |              |                |               |                |         |
|                             | 11h           | –          | vin            |                |                |              |                |               |                |         |
|                             | 12h           | –          | cs2            |                |                |              |                |               |                |         |
|                             | 13h           | –          | cs1            |                |                |              |                |               |                |         |
|                             | 14h           | –          | ocr_l          | v2ovp          | v1ovp          | tsd          | ocr_p          | ov            | ext_clind_ocr  |         |
|                             | 15h           | –          | –              | –              | –              | –            | –              | vchn          | pg_int         |         |

## I<sup>2</sup>C Interface

The I<sup>2</sup>C interface can support 5 V TTL, LVTTTL, 2.5 V and 1.8 V interfaces with two precision SCL and SDA comparators with 1 V thresholds shown in Figure 37. The part cannot support 5 V CMOS levels as there can be some ambiguity in voltage levels.

## I<sup>2</sup>C Compatible Interface

The NCV81599 can support a subset of I<sup>2</sup>C protocol as detailed below. The NCV81599 communicates with the

external processor by means of a serial link using a 400 kHz up to 1.2 MHz I<sup>2</sup>C two-wire interface protocol. The I<sup>2</sup>C interface provided is fully compatible with the Standard, Fast, and High-Speed I<sup>2</sup>C modes. The NCV81599 is not intended to operate as a master controller; it is under the control of the main controller (master device), which controls the clock (pin SCL) and the read or write operations through SDA. The I<sup>2</sup>C bus is an addressable interface (7-bit addressing only) featuring two Read/Write addresses.

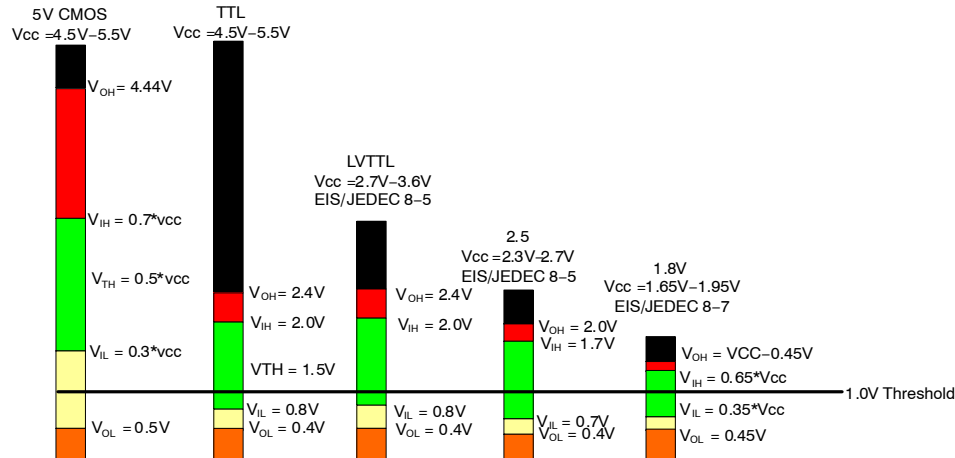


Figure 37. I<sup>2</sup>C Thresholds and Comparator Thresholds

## I<sup>2</sup>C Communication Description

The first byte transmitted is the chip address (with the LSB bit set to 1 for a Read operation, or set to 0 for a Write operation). Following the 1 or 0, the data will be:

- In case of a Write operation, the register address (@REG) pointing to the register for which it will be written is followed by the data that will be written in that location. The writing process is auto-incremental, so the first data will be written in @REG, the contents of @REG are incremented, and the next data byte is placed in the location pointed to @REG + 1..., etc.
- In case of a Read operation, the NCV81599 will output the data from the last register that has been accessed by the last write operation. Like the writing process, the reading process is auto-incremental.

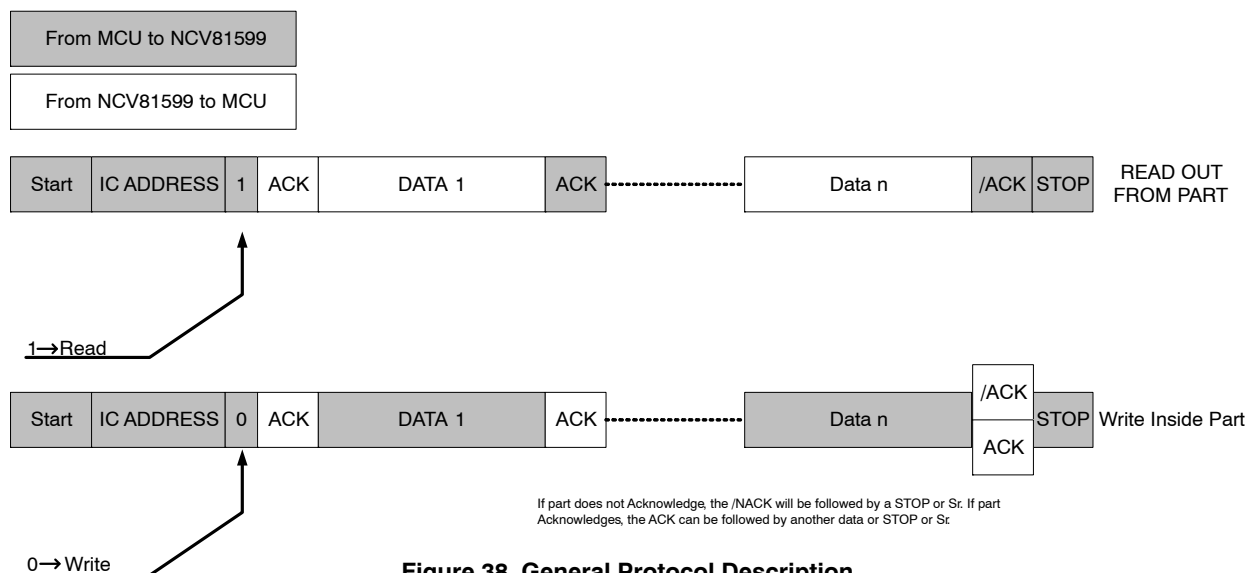


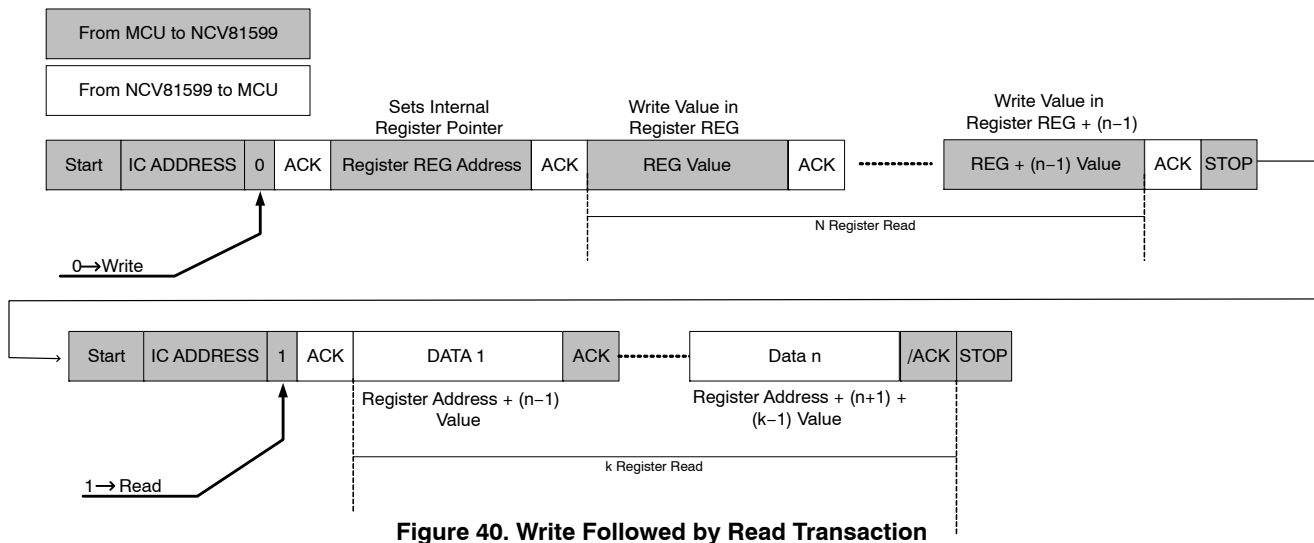
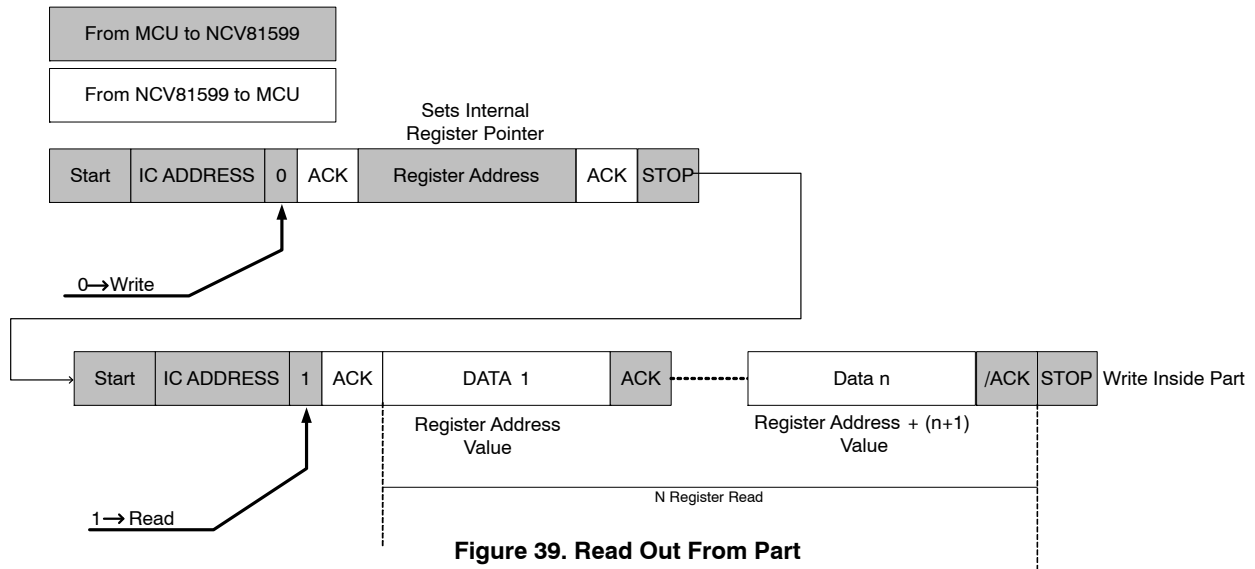
Figure 38. General Protocol Description

## NCV81599, NCP81599

### Read Out from Part

The master will first make a “Pseudo Write” transaction with no data to set the internal address register. Then, a stop

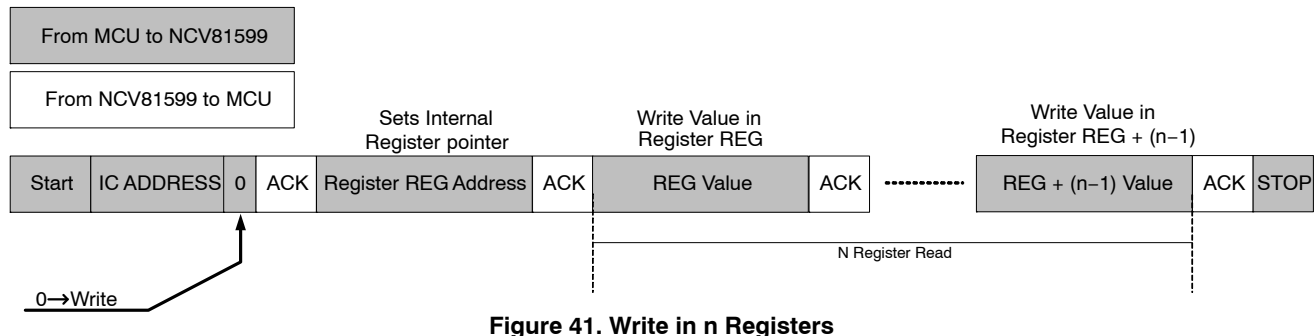
then start or a repeated start will initiate the Read transaction from the register address the initial Write transaction was pointed to:



### Write In Part

Write operation will be achieved by only one transaction. After the chip address, the MCU first data will be the internal

register desired to access, the following data will be the data written in REG, REG + 1, REG + 2, ..., REG + (n-1).



### I<sup>2</sup>C Communication Considerations

- It takes at least 3.3 ms for the digital core to reset all the registers, so it is recommended not to change the register value until at least 3.3 ms after the output voltage finish ramping to a steady state.
- It is recommended to avoid setting reference voltage profile below 0.1 V. When 0 V output is needed, it is recommended to ramp down the output by pulling EN pin low with external circuit or by I<sup>2</sup>C communication in the firmware. Setting output voltage profile to 0 via I<sup>2</sup>C is not recommended.

## DESIGN CONSIDERATIONS

### dv/dt Induced False Turn On

In synchronous buck converters, there is a well-known phenomenon called “low side false turn-on,” or “dv/dt induced turn on”, which can be potentially dangerous for the switch itself and the reliability of the entire converter. The

4-switch buck-boost converter is not exempt from this issue. To make things worse, errors are made when designers simply copy the circuit parameters of a buck converter directly to the boost phase of the 4-switch buck-boost converter.

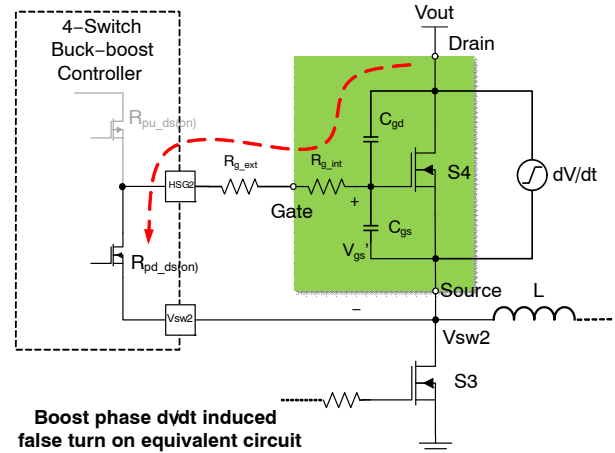
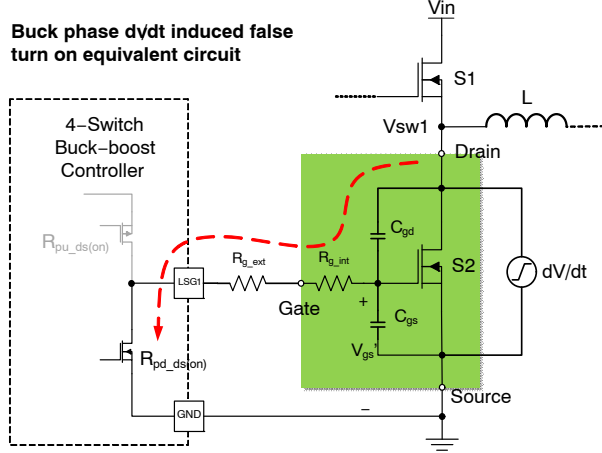


Figure 42. dv/dt Induced False Turn-on Equivalent Circuit of a 4-switch Buck-boost Converter

Figure 42 shows false turn on equivalent circuit of the buck phase and the boost phase at the moment a positive dv/dt transition appears across the drain-to-source junction. The detailed analysis of this phenomenon can be found in Gate Driver Design Considerations for 4-Switch Buck-Boost Converters.

### Select the Switching Power MOSFET

The MOSFETs used in the power stage of the converter should have a maximum drain-to-source voltage rating that exceeds the sum of steady state maximum drain-to-source voltage and the turn-off voltage spike with a considerable margin (20%~50%).

When selecting the switching power MOSFET, the MOSFET gate capacitance should be considered carefully to avoid overloading the 5 V LDO. For one MOSFET, the allowed maximum total gate charge  $Q_g$  can be estimated by Equation 2:

$$Q_g = \frac{I_{\text{driver}}}{f_{\text{sw}}} \quad (\text{eq. 2})$$

where  $I_{\text{driver}}$  is the gate drive current and  $f_{\text{sw}}$  is the switching frequency.

It is recommended to select the MOSFETs with smaller than 3 nF input capacitance ( $C_{\text{iss}}$ ). The gate threshold voltage should be higher than 1.0 V due to the internal adaptive non-overlap gate driver circuit.

In order to prevent dv/dt induced turn-on, the criteria for selecting a rectifying switch is based on the  $Q_{\text{gd}}/Q_{\text{gs(th)}}$  ratio.  $Q_{\text{gs(th)}}$  is the gate-to-source charge before the gate voltage reaches the threshold voltage. Lowering  $C_{\text{gd}}$  will reduce dv/dt induced voltage magnitude. Moreover, it also depends

on  $dt/C_{\text{gs}}$ ,  $V_{\text{ds}}$  and threshold voltage  $V_{\text{th}}$ . One way of interpreting the dv/dt induced turn-on problem is when  $V_{\text{ds}}$  reaches the input voltage, the Miller charge should be smaller than the total charge on  $C_{\text{gs}}$  at the  $V_{\text{th}}$  level, so that the rectifying switches will not be turned on. Then we will have the following relation:

$$V_{\text{gs}} = \frac{C_{\text{gd}}}{C_{\text{gd}} + C_{\text{gs}}} \times V_{\text{ds}} < V_{\text{gs(th)}} \quad (\text{eq. 3})$$

$$Q_{\text{gd}} < Q_{\text{GS(th)}} \quad (\text{eq. 4})$$

We can simply use Equation 4 to evaluate the rectifying device's immunity to dv/dt induced turn on. Ideally, the charge  $Q_{\text{gd}}$  should not be greater than  $1.5 \times Q_{\text{gs(th)}}$  in order to leave enough margin.

### Select Gate Drive Resistors

To increase the converter's dv/dt immunity, the dv/dt control is one approach which is usually related to the gate driver circuit. A first intuitive method is to use higher pull up resistance and gate resistance for the active switch. This would slow down the turn on of the active switch, effectively decreasing the dv/dt. Table 18 shows the recommended value for MOSFETs' gate resistors.

Table 18. RECOMMENDED VALUE for Gate Resistors

| Buck Phase |            | Boost Phase |            |
|------------|------------|-------------|------------|
| HSG1       | (3.3~5.1)Ω | HSG2        | 0Ω         |
| LSG1       | 0Ω         | LSG2        | (3.3~5.1)Ω |

An alternative approach is to add an RC snubber circuit to the switching nodes  $V_{\text{sw1}}$  and  $V_{\text{sw2}}$ . This is the most direct

way to reduce the  $dv/dt$ . The side effect of the above two methods are that losses would be increased because of slow switching speed.

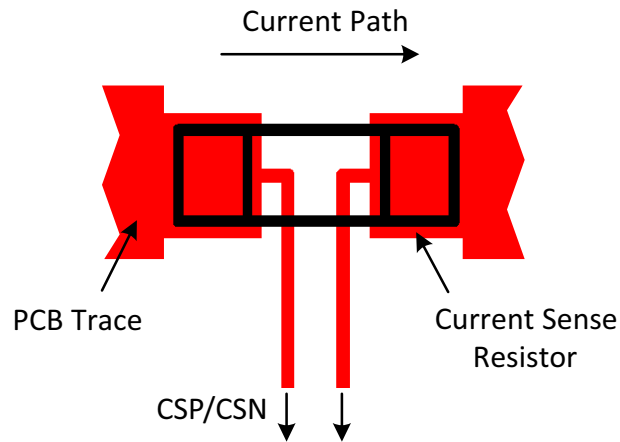
## LAYOUT GUIDELINES

### Electrical Layout Considerations

Good electrical layout is a key to make sure proper operation, high efficiency, and noise reduction.

- **Current Sensing:** Run two dedicated trace with decent width in parallel (close to each other to minimize the loop area) from the two terminals of the input side or output side current sensing resistor to the IC. Place the common-mode RC filter components in general proximity of the controller.

Route the traces into the pads from the inside of the current sensing resistor. The drawing below shows how to rout the traces.



- **Gate Driver:** Run the high side gate, low side gate and switching node traces in a parallel fashion with decent width. Avoid any sensitive analog signal trace from crossing over or getting close. Recommend routing Vsw1/2 trace to high-side MOSFET source pin instead of copper pour area. The controller should be placed close to the switching MOSFETs gate terminals and keep the gate drive signal traces short for a clean MOSFET drive. It's OK to place the controller on the opposite side of the MOSFETs.
- **I2C Communication:** SDA and SCL pins are digital pins. Run SDA and SCL traces in parallel and reduce the loop area. Avoid any sensitive analog signal trace or noise source from crossing over or getting close.
- **V1 Pin:** Input for the internal LDO. Place a decoupling capacitor in general proximity of the controller. Run a dedicated trace from system input bus to the pin and do not route near the switching traces.

- **VCC Decoupling:** Place decoupling caps as close as possible to the controller VCC pin. Place the RC filter connecting with VDRV pin in general proximity of the controller. The filter resistor should be not higher than 10  $\Omega$  to prevent large voltage drop.
- **VDRV Decoupling:** Place decoupling caps as close as possible to the controller VDRV pin.
- **Input Decoupling:** The device should be well decoupled by input capacitors and input loop area should be as small as possible to reduce parasitic inductance, input voltage spike, and noise emission. Usually, a small low-ESL MLCC is placed very close to the input port. Place these capacitors on the same PCB layer with the MOSFETs instead of on different layers and using vias to make the connection.
- **Output Decoupling:** The output capacitors should be as close as possible to the load.
- **Switching Node:** The converter's switching node should be a copper pour to carry the current, but compact because it is also a noise source of electrical and magnetic field radiation. Place the inductor and the switching MOSFETs on the same layer of the PCB.
- **Bootstrap:** The bootstrap cap and an option resistor need to be in general close to the controller and directly connected between pin BST1/2 and pin SW1/2 respectively.
- **Ground:** It would be good to have separated ground planes for PGND and AGND and connect the AGND planes to PGND through a dedicated net tie or 0  $\Omega$  resistor.
- **Voltage Sense:** Route a "quiet" path for the input and output voltage sense. AGND could be used as a remote ground sense when differential sense is preferred.
- **Compensation Network:** The compensation network should be close to the controller. Keep FB trace short to minimize its capacitance to ground.

### Thermal Layout Considerations

Good thermal layout helps power dissipation and junction temperature reduction.

- The exposed pads must be well soldered on the board.
- A four or more layers PCB board with solid ground planes is preferred for better heat dissipation.
- More free vias are welcome to be around IC and underneath the exposed pads to connect the inner ground layers to reduce thermal impedance.
- Use large area copper pour to help thermal conduction and radiation.
- Do not put the inductor too close to the IC, thus the heat sources are distributed.

**ON**



DATE 07 SEP 2018



1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.10 AND 0.20MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN         | NOM  | MAX  |
| A   | 0.80        | 0.90 | 1.00 |
| A1  | ----        | ---- | 0.05 |
| A3  | 0.20 REF    |      |      |
| A4  | 0.10        | ---- | ---- |
| b   | 0.20        | 0.25 | 0.30 |
| D   | 4.90        | 5.00 | 5.10 |
| D2  | 3.00        | 3.10 | 3.20 |
| E   | 4.90        | 5.00 | 5.10 |
| E2  | 3.00        | 3.10 | 3.20 |
| e   | 0.50 BSC    |      |      |
| K   | 0.35        | ---- | ---- |
| L   | 0.30        | 0.40 | 0.50 |
| L3  | ----        | ---- | 0.10 |
| L4  | 0.08 REF    |      |      |

1 ○

XXXXXXXXXX  
XXXXXXXXXX  
AWLYYWW■

■

XXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

[illegible]

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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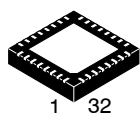
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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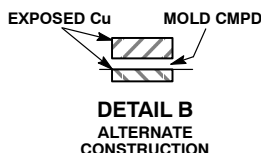
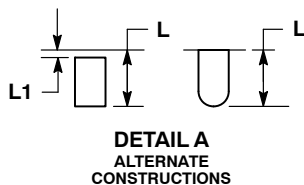
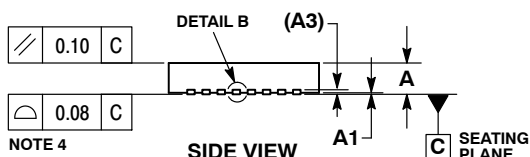
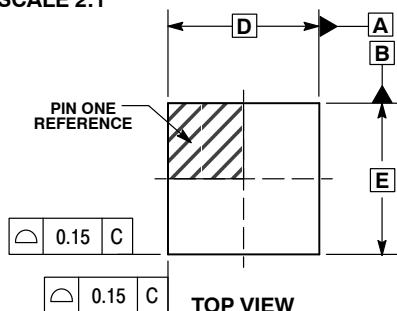
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QFN32 5x5, 0.5P  
CASE 485CE  
ISSUE O

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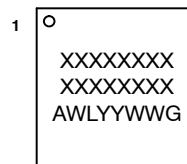


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

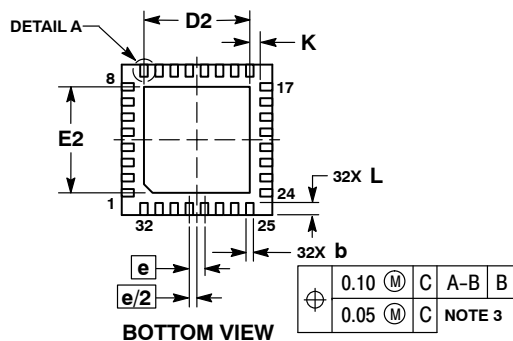
| DIM | MILLIMETERS |      |
|-----|-------------|------|
|     | MIN         | MAX  |
| A   | 0.80        | 1.00 |
| A1  | ---         | 0.05 |
| A3  | 0.20        | REF  |
| b   | 0.20        | 0.30 |
| D   | 5.00        | BSC  |
| D2  | 3.40        | 3.60 |
| E   | 5.00        | BSC  |
| E2  | 3.40        | 3.60 |
| e   | 0.50        | BSC  |
| K   | 0.20        | ---  |
| L   | 0.30        | 0.50 |
| L1  | ---         | 0.15 |

### GENERIC MARKING DIAGRAM\*

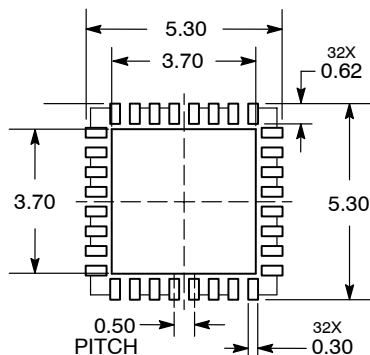


XXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



### RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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